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8/16-bit Microcontroller with Serial Communication Interfaces

1. Description

The TSC80251G2D products are derivatives of the TEMIC Microcontroller family based on the 8/16-bit C251 Architecture. This family of products is tailored to 8/16-bit microcontroller applications requiring an increased instruction throughput, a reduced operating frequency or a larger addressable memory space. The architecture can provide a significant code size reduction when compiling C programs while fully preserving the legacy of C51 assembly routines.

The TSC80251G2D derivatives are pin and software compatible with standard 80C51/Fx/Rx/Rx+ with extended on-chip data memory (1 Kbyte RAM) and up to 256 Kbytes of external code and data. Additionally,

the TSC83251G2D and TSC87251G2D provide on-chip code memory: 32 Kbytes ROM and 32 Kbytes EPROM/ OTPROM respectively.

They provide transparent enhancements to Intel's 8xC251Sx family with an additional Synchronous Serial Link Controller (SSLC supporting I²C, μ Wire and SPI protocols), a Keyboard interrupt interface, a dedicated Baud Rate Generator for UART, and Power Management features.

TSC80251G2D derivatives are optimized for speed and for low power consumption on a wide voltage range.

Note:

This Datasheet provides the technical description of the TSC80251G2D derivatives. For further information on the device usage, please request the TSC80251 Programmer's Guide and the TSC80251G1D Design Guide.

2. Typical Applications

- ISDN Terminals
- High-Speed Modems
- PABX (SOHO)
- Line Cards
- DVD ROM and Players
- Printers
- Plotters

- Scanners
- Banking Machines
- Barcode Readers
- Smart Cards Readers
- High-End Digital Monitors
- High-End Joysticks



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3. Features

- Pin and Software Compatibility with Standard 80C51 Products and 80C51Fx/Rx/Rx+
- Plug-In Replacement of Intel's 8xC251Sx
- C251 core: Intel's MCS[®]251 D-step Compliance
 40-byte register file
 - Registers accessible as Bytes, Words or Dwords
 - Three-stage instruction pipeline
 - 16-bit internal code fetch
- Enriched C51 Instruction Set
 - 16-bit and 32-bit ALU
 - Compare and conditional jump instructions
 - Expanded set of move instructions
- Linear Addressing
- 1 Kbyte of On-Chip RAM
- External Memory Space (Code/Data) Programmable from 64 Kbytes to 256 Kbytes
- TSC87251G2D: 32 Kbytes of On-Chip EPROM/ OTPROM
 - SINGLE PULSE Programming Algorithm
- TSC83251G2D: 32 Kbytes of On-Chip Masked ROM
- TSC80251G2D: ROMless Version
- Four 8-bit Parallel I/O Ports (Ports 0, 1, 2 and 3 of the standard 80C51)
- Serial I/O Port: full duplex UART (80C51 compatible) with independent Baud Rate Generator
- SSLC: Synchronous Serial Link Controller
 - I²C multi-master protocol
 - $\mu Wire$ and SPI master and slave protocols
- Three 16-bit Timers/Counters (Timers 0, 1 and 2 of the standard 80C51)
- EWC: Event and Waveform Controller
 - Compatible with Intel's Programmable Counter Array (PCA)
 - Common 16-bit timer/counter reference with four possible clock sources (Fosc/4, Fosc/12, Timer 1 and external input)
 - Five modules, each with four programmable modes:
 - 16-bit software timer/counter
 - 16-bit timer/counter capture input and software pulse measurement
 - High-speed output and 16-bit software pulse width modulation (PWM)
 - 8-bit hardware PWM without overhead

- 16-bit watchdog timer/counter capability
- Secure 14-bit Hardware Watchdog Timer
- Power Management
 - Power-On reset (integrated on the chip)
 - Power-Off flag (cold and warm resets)
 - Software programmable system clock
 - Idle mode
 - Power-Down mode
- Keyboard Interrupt Interface on Port 1
- Non Maskable Interrupt Input (NMI)
- Real-Time Wait States Inputs (WAIT#/AWAIT#)
- ONCE mode and full speed Real-Time In-Circuit Emulation support (Third Party Vendors)
- High Speed Versions:
- 4.5 to 5.5 V
- 16 MHz and 24 MHz
- Typical operating current: 35 mA @ 24 MHz 24 mA @ 16 MHz
- Typical power-down current: 2 µA
- Low Voltage Version:
- 2.7 to 5.5 V
- 16 MHz
- Typical operating current: 11 mA @ 3V
- Typical power-down current: 1 µA
- Temperature Ranges:
 - Commercial (0°C to +70°C)
 - Industrial (-40°C to +85°C)
 - Option: extended range (-55°C to +125°C)
- Packages:
 - PDIL 40, PLCC 44 and VQFP 44
 - CDIL 40 and CQPJ 44 with window
 - Options: known good dice and ceramic packages



4. Block Diagram

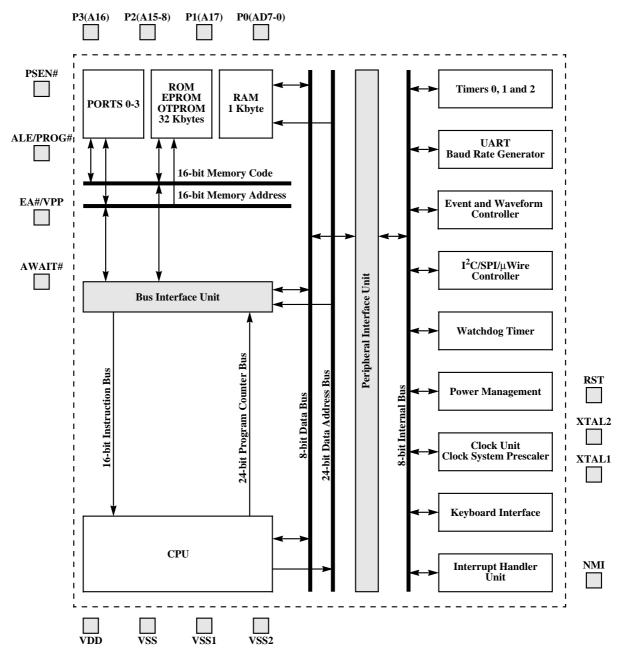
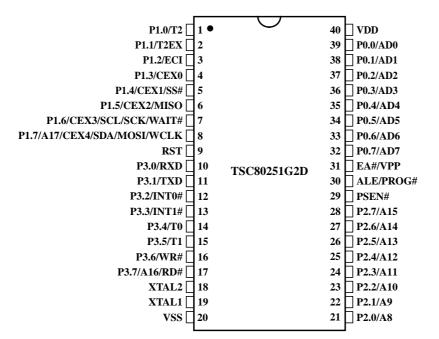


Figure 1. TSC80251G2D Block Diagram

5. Pin Description

5.1 Pinout





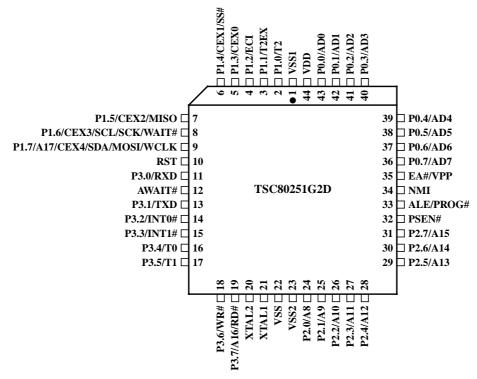


Figure 3. TSC80251G2D 44-pin PLCC Package





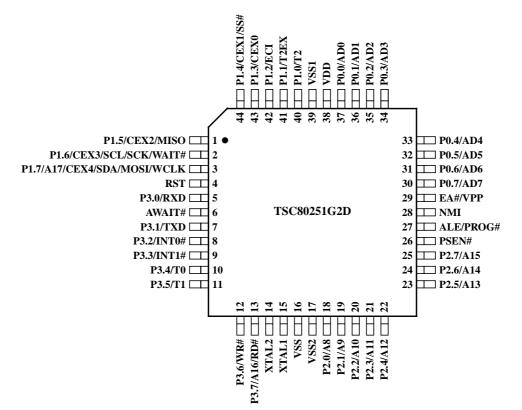


Figure 4. TSC80251G2D 44-pin VQFP Package	Figure 4.	TSC80251G2D	44-pin	VQFP	Package
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DIP	PLCC	VQFP	Name	DIP	PLCC	VQFP	Name
	1	39	VSS1		23	17	VSS2
1	2	40	P1.0/T2	21	24	18	P2.0/A8
2	3	41	P1.1/T2EX	22	25	19	P2.1/A9
3	4	42	P1.2/ECI	23	26	20	P2.2/A10
4	5	43	P1.3/CEX0	24	27	21	P2.3/A11
5	6	44	P1.4/CEX1/SS#	25	28	22	P2.4/A12
6	7	1	P1.5/CEX2/MISO	26	29	23	P2.5/A13
7	8	2	P1.6/CEX3/SCL/SCK/WAIT#	27	30	24	P2.6/A14
8	9	3	P1.7/A17/CEX4/SDA/MOSI/WCLK	28	31	25	P2.7/A15
9	10	4	RST	29	32	26	PSEN#
10	11	5	P3.0/RXD	30	33	27	ALE/PROG#
	12	6	AWAIT#		34	28	NMI
11	13	7	P3.1/TXD	31	35	29	EA#/VPP
12	14	8	P3.2/INT0#	32	36	30	P0.7/AD7
13	15	9	P3.3/INT1#	33	37	31	P0.6/AD6
14	16	10	P3.4/T0	34	38	32	P0.5/AD5
15	17	11	P3.5/T1	35	39	33	P0.4/AD4
16	18	12	P3.6/WR#	36	40	34	P0.3/AD3
17	19	13	P3.7/A16/RD#	37	41	35	P0.2/AD2
18	20	14	XTAL2	38	42	36	P0.1/AD1
19	21	15	XTAL1	39	43	37	P0.0/AD0
20	22	16	VSS	40	44	38	VDD

Table 1. TSC80251G2D Pin Assignment

5.2 Signals

Table 2. Product Name Signal Descriptions

Signal Name	Туре	Description	Alternate Function	
A17	0	 18th Address Bit Output to memory as 18th external address bit (A17) in extended bus applications, depending on the values of bits RD0 and RD1 in UCONFIG0 byte (see Table 13, Page 15). 	P1.7	
A16	0	17 th Address Bit Output to memory as 17th external address bit (A16) in extended bus applications, depending on the values of bits RD0 and RD1 in UCONFIG0 byte (see Table 13, Page 15).	P3.7	
A15:8 ⁽¹⁾	0	Address Lines Upper address lines for the external bus.	P2.7:0	
AD7:0 ⁽¹⁾	I/O	Address/Data Lines Multiplexed lower address lines and data for the external memory.	P0.7:0	
ALE	0	Address Latch Enable ALE signals the start of an external bus cycle and indicates that valid address information are available on lines A16/A17 and A7:0. An external latch can use ALE to demultiplex the address from address/data bus.		
AWAIT#	Ι	 Real-time Asynchronous Wait States Input When this pin is active (low level), the memory cycle is stretched until it becomes high. When using the Product Name as a pin-for-pin replacement for a 8xC51 product, AWAIT# can be unconnected without loss of compatibility or power consumption increase (on-chip pull-up). Not available on DIP package. 		
CEX4:0	I/O	PCA Input/Output pins CEXx are input signals for the PCA capture mode and output signals for the PCA compare and PWM modes.		
EA#	I	External Access Enable EA# directs program memory accesses to on-chip or off-chip code memory. For EA#= 0, all program memory accesses are off-chip. For EA#= 1, an access is on-chip ROM if the address is within the range of the on-chip ROM; otherwise the access is off-chip. The value of EA# is latched at reset. For devices without ROM on-chip, EA# must be strapped to ground.		
ECI	0	PCA External Clock input ECI is the external clock input to the 16-bit PCA timer.	P1.2	
MISO	I/O	SPI Master Input Slave Output line When SPI is in master mode, MISO receives data from the slave peripheral. When SPI is in slave mode, MISO outputs data to the master controller.	P1.5	
MOSI	I/O	SPI Master Output Slave Input line When SPI is in master mode, MOSI outputs data to the slave peripheral. When SPI is in slave mode, MOSI receives data from the master controller.	P1.7	
INT1:0#	I	 External Interrupts 0 and 1 INT1#/INT0# inputs set IE1:0 in the TCON register. If bits IT1:0 in the TCON register are set, bits IE1:0 are set by a falling edge on INT1#/INT0#. If bits IT1:0 are cleared, bits IE1:0 are set by a low level on INT1#/INT0#. 		
NMI	I	 Non Maskable Interrupt Holding this pin high for 24 oscillator periods triggers an interrupt. When using the Product Name as a pin-for-pin replacement for a 8xC51 product, NMI can be unconnected without loss of compatibility or power consumption increase (on-chip pull-down). Not available on DIP package. 		
P0.0:7	I/O	 Port 0 P0 is an 8-bit open-drain bidirectional I/O port. Port 0 pins that have 1s written to them float and can be used as high impedance inputs. To avoid any paraitic current consumption, Floating P0 inputs must be polarized to V_{DD} or V_{SS}. 	AD7:0	



Signal Name	Туре	Description	Alternate Function		
P1.0:7	I/O	Port 1 P1 is an 8-bit bidirectional I/O port with internal pull-ups. P1 provides interrupt capability for a keyboard interface.			
P2.0:7	I/O	Port 2 P2 is an 8-bit bidirectional I/O port with internal pull-ups.	A15:8		
P3.0:7	I/O	Port 3 P3 is an 8-bit bidirectional I/O port with internal pull-ups.			
PROG#	Ι	Programming Pulse input The programming pulse is applied to this input for programming the on-chip EPROM/ OTPROM.			
PSEN#	0	Program Store Enable/Read signal output PSEN# is asserted for a memory address range that depends on bits RD0 and RD1 in UCONFIG0 byte (see Table 13, Page 15).			
RD#	0	Read or 17 th Address Bit (A16) Read signal output to external data memory depending on the values of bits RD0 and RD1 in UCONFIG0 byte (see Table 13, Page 15).	P3.7		
RST	I	$\begin{array}{c} \textbf{Reset input to the chip} \\ & Holding this pin high for 64 oscillator periods while the oscillator is running resets the device. The Port pins are driven to their reset conditions when a voltage greater than V_{IH1} is applied, whether or not the oscillator is running. This pin has an internal pull-down resistor which allows the device to be reset by connecting a capacitor between this pin and VDD. Asserting RST when the chip is in Idle mode or Power-Down mode returns the chip to normal operation. \end{array}$			
RXD	I/O	Receive Serial Data RXD sends and receives data in serial I/O mode 0 and receives data in serial I/O modes 1, 2 and 3.	P3.0		
SCL	I/O	I ² C Serial Clock When I ² C controller is in master mode, SCL outputs the serial clock to slave peripherals. When I ² C controller is in slave mode, SCL receives clock from the master controller.	P1.6		
SCK	I/O	SPI Serial Clock When SPI is in master mode, SCK outputs clock to the slave peripheral. When SPI is in slave mode, SCK receives clock from the master controller.	P1.6		
SDA	I/O	I ² C Serial Data SDA is the bidirectional I ² C data line.	P1.7		
SS#	Ι	SPI Slave Select Input When in Slave mode, SS# enables the slave mode.	P1.4		
T1:0	I/O	Timer 1:0 External Clock Inputs When timer 1:0 operates as a counter, a falling edge on the T1:0 pin increments the count.			
T2	I/O	Timer 2 Clock Input/Output I For the timer 2 capture mode, T2 is the external clock input. For the Timer 2 clock-out mode, T2 is the clock output.			
T2EX	I	Timer 2 External Input In timer 2 capture mode, a falling edge initiates a capture of the timer 2 registers. In autoreload mode, a falling edge causes the timer 2 register to be reloaded. In the up-down counter mode, this signal determines the count direction: 1= up, 0= down.			
TXD	0	Transmit Serial Data TXD outputs the shift clock in serial I/O mode 0 and transmits data in serial I/O modes 1, 2 and 3.	P3.1		
VDD	PWR	Digital Supply Voltage Connect this pin to +5V or +3V supply voltage.			
VPP	Ι	Programming Supply Voltage The programming supply voltage is applied to this input for programming the on-chip EPROM/ OTPROM.			

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Signal Name	Туре	Description	Alternate Function		
VSS	GND	Circuit Ground Connect this pin to ground.			
VSS1	GND Secondary Ground 1 This ground is provided to reduce ground bounce and improve power supply bypassing. Connection of this pin to ground is recommended. However, when using the TSC80251G2D as a pin-for-pin replacement for a 8xC51 product, VSS1 can be unconnected without loss of compatibility. Not available on DIP package.				
VSS2	GND	 Secondary Ground 2 This ground is provided to reduce ground bounce and improve power supply bypassing. Connection of this pin to ground is recommended. However, when using the TSC80251G2D as a pin-for-pin replacement for a 8xC51 product, VSS2 can be unconnected without loss of compatibility. Not available on DIP package. 			
WAIT#	I	Real-time Synchronous Wait States Input The real-time WAIT# input is enabled by setting RTWE bit in WCON (S:A7h). During bus cycles, the external memory system can signal 'system ready' to the microcontroller in real time by controlling the WAIT# input signal.	P1.6		
WCLK	0	Wait Clock Output The real-time WCLK output is enabled by setting RTWCE bit in WCON (S:A7h). When enabled, the WCLK output produces a square wave signal with a period of one half the oscillator frequency.	P1.7		
WR#	0	Write Write signal output to external memory.	P3.6		
XTAL1	I	Input to the on-chip inverting oscillator amplifier To use the internal oscillator, a crystal/resonator circuit is connected to this pin. If an external oscillator is used, its output is connected to this pin. XTAL1 is the clock source for internal timing.			
XTAL2	0	Output of the on-chip inverting oscillator amplifier To use the internal oscillator, a crystal/resonator circuit is connected to this pin. If an external oscillator is used, leave XTAL2 unconnected.			

Note:

1. The description of A15:8/P2.7:0 and AD7:0/P0.7:0 are for the Non-Page mode chip configuration. If the chip is configured in Page mode operation, port 0 carries the lower address bits (A7:0) while port 2 carries the upper address bits (A15:8) and the data (D7:0).



6. Address Spaces

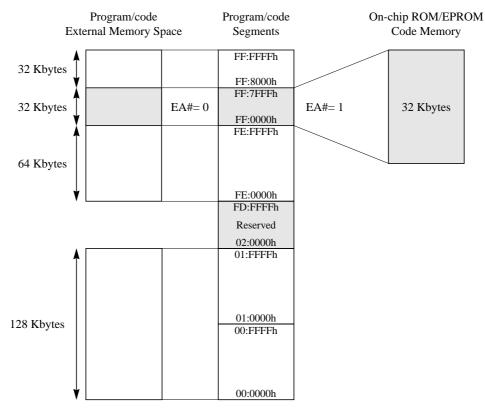
The TSC80251G2D derivatives implement four different address spaces:

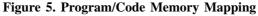
- On-chip ROM program/code memory (not present in ROMless devices)
- On-chip RAM data memory
- Special Function Registers (SFRs)
- Configuration array

6.1 Program/Code Memory

The TSC83251G2D and TSC87251G2D implement 32 Kbytes of on-chip program/code memory. Figure 5 shows the split of the internal and external program/code memory spaces. If EA# is tied to a high level, the 32-Kbyte on-chip program memory is mapped in the lower part of segment FF: where the C251 core jumps after reset. The rest of the program/code memory space is mapped to the external memory. If EA# is tied to a low level, the internal program/code memory is not used and all the accesses are directed to the external memory.

The TSC83251G2D products provide the internal program/code memory in a masked ROM memory while the TSC87251G2D products provide it in an EPROM memory. For the TSC80251G2D products, there is no internal program/code memory and EA# must be tied to a low level.





Notes:

Special care should be taken when the Program Counter (PC) increments:

- 1. If the program executes exclusively from on-chip code memory (not from external memory), beware of executing code from the upper eight bytes of the on-chip ROM (FF:7FF8h-FF:7FFFh). Because of its pipeline capability, the TSC80251G2D derivative may attempt to prefetch code from external memory (at an address above FF:7FFFh) and thereby disrupt I/O Ports 0 and 2. Fetching code constants from these 8 bytes does not affect Ports 0 and 2.
- 2. When PC reaches the end of segment FF:, it loops to the reset address FF:0000h (for compatibility with the C51 Architecture). When PC increments beyond the end of segment FE:, it continues at the reset address FF:0000h (linearity). When PC increments beyond the end of segment 01:, it loops to the beginning of segment 00: (this prevents from its going into the reserved area).

6.2 Data Memory

The TSC80251G2D derivatives implement 1 Kbyte of on-chip data RAM. Figure 6 shows the split of the internal and external data memory spaces. This memory is mapped in the data space just over the 32 bytes of registers area (see TSC80251 Programmers' Guide). Hence, the part of the on-chip RAM located from 20h to FFh is bit addressable. This on-chip RAM is not accessible through the program/code memory space.

For faster computation with the on-chip ROM/EPROM code of the TSC83251G2D/TSC87251G2D, its upper 16 Kbytes are also mapped in the upper part of the region 00: if the On-Chip Code Memory Map configuration bit is cleared (EMAP# bit in UCONFIG1 byte, see Figure 8). However, if EA# is tied to a low level, the TSC80251G2D derivative is running as a ROMless product and the code is actually fetched in the corresponding external memory (i.e. the upper 16 Kbytes of the lower 32 Kbytes of the segment FF:). If EMAP# bit is set, the on-chip ROM is not accessible through the region 00:.

All the accesses to the portion of the data space with no on-chip memory mapped onto are redirected to the external memory.

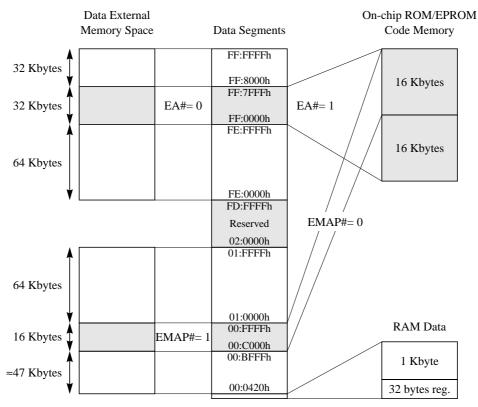


Figure 6. Data Memory Mapping

6.3 Special Function Registers

The Special Function Registers (SFRs) of the TSC80251G2D derivatives fall into the categories detailed in Table 3 to Table 11.

SFRs are placed in a reserved on-chip memory region S: which is not represented in the data memory mapping (Figure 6). The relative addresses within S: of these SFRs are provided together with their reset values in Table 12. They are upward compatible with the SFRs of the standard 80C51 and the Intel's 80C251Sx family. In this table, the C251 core registers are identified by Note 1 and are described in the TSC80251 Programmer's Guide. The other SFRs are described in the TSC80251G1D Design Guide. All the SFRs are bit-addressable using the C251 instruction set.



Table 3. C251 Core SFRs

Mnemonic	Name	Mnemonic	Name
ACC ⁽¹⁾	Accumulator	SPH ⁽¹⁾	Stack Pointer High - MSB of SPX
B ⁽¹⁾	B Register	DPL ⁽¹⁾	Data Pointer Low byte - LSB of DPTR
PSW	Program Status Word	DPH ⁽¹⁾	Data Pointer High byte - MSB of DPTR
PSW1	Program Status Word 1	DPXL ⁽¹⁾	Data Pointer Extended Low byte of DPX - Region
SP ⁽¹⁾	Stack Pointer - LSB of SPX		number

Note: 1. These SFRs can also be accessed by their corresponding registers in the register file.

Table 4. I/O Port SFRs

Mnemonic	Name	Mnemonic	Name
P0	Port 0	P2	Port 2
P1	Port 1	P3	Port 3

Table 5. Timers SFRs

Mnemonic	Name	Mnemonic	Name
TL0	Timer/Counter 0 Low Byte	TMOD	Timer/Counter 0 and 1 Modes
TH0	Timer/Counter 0 High Byte	T2CON	Timer/Counter 2 Control
TL1	Timer/Counter 1 Low Byte	T2MOD	Timer/Counter 2 Mode
TH1	Timer/Counter 1 High Byte	RCAP2L	Timer/Counter 2 Reload/Capture Low Byte
TL2	Timer/Counter 2 Low Byte	RCAP2H	Timer/Counter 2 Reload/Capture High Byte
TH2	Timer/Counter 2 High Byte	WDTRST	WatchDog Timer Reset
TCON	Timer/Counter 0 and 1 Control		

Table 6. Serial I/O Port SFRs

Mnemonic	Name	Mnemonic	Name
SCON	Serial Control	SADDR	Slave Address
SBUF	Serial Data Buffer	BRL	Baud Rate Reload
SADEN	Slave Address Mask	BDRCON	Baud Rate Control

Table 7. SSLC SFRs

Mnemonic	Name	Mnemonic	Name
SSCON	Synchronous Serial control	SSADR	Synchronous Serial Address
SSDAT	Synchronous Serial Data	SSBR	Synchronous Serial Bit Rate
SSCS	Synchronous Serial Control and Status		

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Table 8.	Event	Waveform	Control	SFRs	
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Mnemonic	Name	Mnemonic	Name
CCON	EWC-PCA Timer/Counter Control	CCAP0L	EWC-PCA Compare Capture Module 0 Low Regi
CMOD	EWC-PCA Timer/Counter Mode	CCAP1L	EWC-PCA Compare Capture Module 1 Low Regi
CL	EWC-PCA Timer/Counter Low Register	CCAP2L	EWC-PCA Compare Capture Module 2 Low Regi
СН	EWC-PCA Timer/Counter High Register	CCAP3L	EWC-PCA Compare Capture Module 3 Low Regi
CCAPM0	EWC-PCA Timer/Counter Mode 0	CCAP4L	EWC-PCA Compare Capture Module 4 Low Regi
CCAPM1	EWC-PCA Timer/Counter Mode 1	ССАРОН	EWC-PCA Compare Capture Module 0 High Regi
CCAPM2	EWC-PCA Timer/Counter Mode 2	CCAP1H	EWC-PCA Compare Capture Module 1 High Register
CCAPM3	EWC-PCA Timer/Counter Mode 3	CCAP2H	EWC-PCA Compare Capture Module 2 High Register
CCAPM4	EWC-PCA Timer/Counter Mode 4	ССАРЗН	EWC-PCA Compare Capture Module 3 High Register
		CCAP4H	EWC-PCA Compare Capture Module 4 High Regi

Table 9. System Management SFRs

Mnemonic	Name	Mnemonic	Name
PCON	Power Control	CKRL	Clock Reload
POWM	Power Management	WCON	Synchronous Real-Time Wait State Control

Table 10. Interrupt SFRs

Mnemonic	nic Name		Name
IE0	Interrupt Enable Control 0	IPL0	Interrupt Priority Control Low 0
IE1	Interrupt Enable Control 1	IPH1	Interrupt Priority Control High 1
IPH0	Interrupt Priority Control High 0	IPL1	Interrupt Priority Control Low 1

Table 11. Keyboard Interface SFRs

Mnemonic	Name	Mnemonic	Name
P1IE	Port 1 Input Interrupt Enable	P1LS	Port 1 Level Selection
P1F	Port 1 Flag		-



	0/8	1/9	2/A	3/B	4/C	5/D	6/E	7/F	_
F8h		CH 0000 0000	CCAP0H 0000 0000	CCAP1H 0000 0000	CCAP2H 0000 0000	CCAP3H 0000 0000	CCAP4H 0000 0000		FFh
F0h	B ⁽¹⁾ 0000 0000								F7h
E8h		CL 0000 0000	CCAP0L 0000 0000	CCAP1L 0000 0000	CCAP2L 0000 0000	CCAP3L 0000 0000	CCAP4L 0000 0000		EFh
E0h	ACC ⁽¹⁾ 0000 0000								E7h
D8h	CCON 00X0 0000	CMOD 00XX X000	CCAPM0 X000 0000	CCAPM1 X000 0000	CCAPM2 X000 0000	CCAPM3 X000 0000	CCAPM4 X000 0000		DFh
D0h	PSW ⁽¹⁾ 0000 0000	PSW1 ⁽¹⁾ 0000 0000							D7h
C8h	T2CON 0000 0000	T2MOD XXXX XX00	RCAP2L 0000 0000	RCAP2H 0000 0000	TL2 0000 0000	TH2 0000 0000			CFh
C0h									C7h
B8h	IPL0 X000 0000	SADEN 0000 0000					SPH ⁽¹⁾ 0000 0000		BFh
B0h	P3 1111 1111	IE1 XX0X XXX0	IPL1 XX0X XXX0	IPH1 XX0X XXX0				IPH0 X000 0000	B7h
A8h	IE0 0000 0000	SADDR 0000 0000							AFh
A0h	P2 1111 1111						WDTRST 1111 1111	WCON XXXX XX00	A7h
98h	SCON 0000 0000	SBUF XXXX XXXX	BRL 0000 0000	BDRCON XXX0 0000	P1LS 0000 0000	P1IE 0000 0000	P1F 0000 0000		9Fh
90h	P1 1111 1111		SSBR 0000 0000	SSCON (2)	SSCS (3)	SSDAT 0000 0000	SSADR 0000 0000		97h
88h	TCON 0000 0000	TMOD 0000 0000	TL0 0000 0000	TL1 0000 0000	TH0 0000 0000	TH1 0000 0000	CKRL 0000 1000	POWM 0XXX XXXX	8Fh
80h	P0 1111 1111	SP ⁽¹⁾ 0000 0111	DPL ⁽¹⁾ 0000 0000	DPH ⁽¹⁾ 0000 0000	DPXL ⁽¹⁾ 0000 0001			PCON 0000 0000	87h
	0/8	1/9	2/A	3/B	4/C	5/D	6/E	7/F	-

Table 12. SFR Addresses and Reset Values

Reserved

Notes:

1. These registers are described in the TSC80251 Programmer's Guide (C251 core registers).

2. In I²C and SPI modes, SSCON is splitted in two separate registers. SSCON reset value is 0000 0000 in I²C mode and 0000 0100 in SPI mode.

3. In read and write modes, SSCS is splitted in two separate registers. SSCS reset value is 1111 1000 in read mode and 0000 0000 in write mode.

6.4 Configuration Bytes

The TSC80251G2D derivatives provide user design flexibility by configuring certain operating features at device reset. These features fall into the following categories:

- external memory interface (Page mode, address bits, programmed wait states and the address range for RD#, WR#, and PSEN#)
- source mode/binary mode opcodes
- selection of bytes stored on the stack by an interrupt
- mapping of the upper portion of on-chip code memory to region 00:

Two user configuration bytes UCONFIG0 (see Figure 7) and UCONFIG1 (see Figure 8) provide the information.

When EA# is tied to a low level, the configuration bytes are fetched from the external address space. The TSC80251G2D derivatives reserve the top eight bytes of the memory address space (FF:FFF8h-FF:FFFFh) for an external 8-byte configuration array. Only two bytes are actually used: UCONFIG0 at FF:FFF8h and UCONFIG1 at FF:FFF9h.

For the mask ROM devices, configuration information is stored in on-chip memory (see ROM Verifying). When EA# is tied to a high level, the configuration information is retrieved from the on-chip memory instead of the external address space and there is no restriction in the usage of the external memory.

UCONFIG0

Configuration Byte 0

7	6	5	4	3	2	1	0
-	WSA1#	WSA0#	XALE#	RD1	RD0	PAGE#	SRC
Bit Number	Bit Mnemonic			Desc	ription		
7	-	Reserved Set this b	it when writing t	o UCONFIG0.			
6	WSA1#		number of wait ns except 01:).	states for RD#, WF	·	gnals for external m	nemory accesses
5	WSA0#	0 0 1 1	0 1 0 1	3 2 1 0			
4	XALE#		extend the duration	on of the ALE puls on of the ALE puls		3·T _{OSC.}	
3	RD1	Memory Signa		16-bit external add	lrass bus and the	usage of PD# W	P# and DSEN#
2	RD0	1 2	ee Table 13).	10-bit externar add	iress bus and the	usage of $RD\pi$, wh	
1	PAGE#		select the faster H	Page mode with A1 mode ⁽²⁾ with A15:			
0	SRC	Clear to s	Binary Mode Se select the binary ect the source m	mode.			

Notes:

1. UCONFIG0 is fetched twice so it can be properly read both in Page or Non-Page modes. If P2.1 is cleared during the first data fetch, a Page mode configuration is used, otherwise the subsequent fetches are performed in Non-Page mode.

2. This selection provides compatibility with the standard 80C51 hardware which is multiplexing the address LSB and the data on Port 0.

Figure 7. Configuration Byte 0



UCONFIG1

Configuration Byte 1

7	6	5	4	3	2	1	0
CSIZE	-	-	INTR	WSB	WSB1#	WSB0#	EMAP#
Bit Number	Bit Mnemonic			Dese	cription		
7	CSIZE TSC87251G2D		elect 16 Kbyte	e bit ⁽¹⁾ es of on-chip code n of on-chip code men			
1	- TSC80251G2D TSC83251G2D	Reserved Set this b	it when writin	g to UCONFIG1.			
6	-	Reserved Set this b	it when writin	g to UCONFIG1.			
5	-	Reserved Set this bi	it when writin	g to UCONFIG1.			
4	INTR		hat the interrupt	pts push two bytes o s push four bytes ont	· · ·	•	U
3	WSB		generate one w	vait state for memory or memory region 01	U		
2	WSB1#	Wait State B Select the (only regi <u>WSB1#</u>	number of wa	ait states for RD#, W <u>Number of Wait S</u>		gnals for external	memory access
1	WSB0#	0 0 1 1	0 1 0 1	3 2 1 0			
0	EMAP#	space (at	nap the upper 00:C000h-00:H	16 Kbytes of on-ch			

Notes:

1. The CSIZE is only available on EPROM/OTPROM products.

2. Two or four bytes are transparently popped according to INTR when using the RETI instruction. INTR must be set if interrupts are used with code executing outside region FF:.

3. Use only for Step A compatibility; set this bit when WSB1:0# are used.

Figure 8. Configuration Byte 1

Table 13. Address	Ranges and	Usage of RD#	WR# and	PSEN# Signals
Table 15. Address	Kanges and	Usage of KD#,	WN# anu	FSEIN# Signais

RD1	RD0	P1.7	P3.7/RD#	PSEN#	WR#	External Memory
0	0	A17	A16	Read signal for all external memory locations	Write signal for all external memory locations	256 Kbytes
0	1	I/O pin	A16	Read signal for all external memory locations	Write signal for all external memory locations	128 Kbytes
1	0	I/O pin	I/O pin	Read signal for all external memory locations	Write signal for all external memory locations	64 Kbytes
1	1	I/O pin	Read signal for regions 00: and 01:	Read signal for regions FE: and FF:	Write signal for all external memory locations	$2 \times 64 \text{ Kbytes}^{(1)}$

Note:

1. This selection provides compatibility with the standard 80C51 hardware which has separate external memory spaces for data and code.



7. Instruction Set Summary

This section contains tables that summarize the instruction set. For each instruction there is a short description, its length in bytes, and its execution time in states (one state time is equal to two system clock cycles). There are two concurrent processes limiting the effective instruction throughput:

- Instruction Fetch
- Instruction Execution

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Table 20 to Table 34 assume code executing from on-chip memory, then the CPU is fetching 16-bit at a time and this is never limiting the execution speed.

If the code is fetched from external memory, a pre-fetch queue will store instructions ahead of execution to optimize the memory bandwidth usage when slower instructions are executed. However, the effective speed may be limited depending on the average size of instructions (for the considered section of the program flow). The maximum average instruction throughput is provided by Table 14 depending on the external memory configuration (from Page Mode to Non-Page Mode and the maximum number of wait states). If the average size of instructions is not an integer, the maximum effective throughput is found by pondering the number of states for the neighbor integer values.

Average size of Page Mode		Non-Page Mode (states)						
Instructions (bytes)	(states)	0 Wait State	1 Wait State	2 Wait States	3 Wait States	4 Wait States		
1	1	2	3	4	5	6		
2	2	4	6	8	10	12		
3	3	6	9	12	15	18		
4	4	8	12	16	20	24		
5	5	10	15	20	25	30		

Table 14. Minimum Number of States per Instruction for given Average Sizes

If the average execution time of the considered instructions is larger than the number of states given by Table 14, this larger value will prevail as the limiting factor. Otherwise, the value from Table 14 must be taken. This is providing a fair estimation of the execution speed but only the actual code execution can provide the final value.

7.1 Notation for Instruction Operands

Table 15 to Table 19 provide notation for Instruction Operands.

Table 15. Notation for Direct Addressing

Direct Address	Description	C251	C51
dir8	A direct 8-bit address. This can be a memory address (00h-7Fh) or a SFR address (80h-FFh). It is a byte (default), word or double word depending on the other operand.	1	1
dir16	A 16-bit memory address (00:0000h-00:FFFFh) used in direct addressing.	1	

Table 16. Notation for Immediate Addressing

Immediate Address	Description	C251	C51
#data	An 8-bit constant that is immediately addressed in an instruction	1	✓
#data16	A 16-bit constant that is immediately addressed in an instruction	1	
#0data16 #1data16	A 32-bit constant that is immediately addressed in an instruction. The upper word is filled with zeros (#0data16) or ones (#1data16).	1	
#short	A constant, equal to 1, 2, or 4, that is immediately addressed in an instruction.	1	

Direct Address	Description	C251	C51
bit51	A directly addressed bit (bit number= 00h-FFh) in memory or an SFR. Bits 00h-7Fh are the 128 bits in byte locations 20h-2Fh in the on-chip RAM. Bits 80h-FFh are the 128 bits in the 16 SFRs with addresses that end in 0h or 8h, S:80h, S:88h, S:90h,, S:F0h, S:F8h.		✓
bit	A directly addressed bit in memory locations 00:0020h-00:007Fh or in any defined SFR.	1	

Table 17. Notation for Bit Addressing

Table 18. Notation for Destination in Control Instructions

Direct Address	Description	C251	C51
rel	A signed (two's complement) 8-bit relative address. The destination is -128 to +127 bytes relative to the next instruction's first byte.	1	1
addr11	An 11-bit target address. The target is in the same 2-Kbyte block of memory as the next instruction's first byte.		1
addr16	A 16-bit target address. The target can be anywhere within the same 64-Kbyte region as the next instruction's first byte.		1
addr24	A 24-bit target address. The target can be anywhere within the 16-Mbyte address space.	1	

Table 19. Notation for Register Operands

Register	Description	C251	C51
@Ri	A memory location (00h-FFh) addressed indirectly via byte registers R0 or R1		1
Rn n	Byte register R0-R7 of the currently selected register bank Byte register index: n= 0-7		1
Rm Rmd Rms m, md, ms	Byte register R0-R15 of the currently selected register file Destination register Source register Byte register index: m, md, ms= 0-15	<i>√</i>	
WRj WRjd WRjs @WRj @WRj +dis16 j, jd, js	Word register WR0, WR2,, WR30 of the currently selected register file Destination register Source register A memory location (00:0000h-00:FFFFh) addressed indirectly through word register WR0- WR30, is the target address for jump instructions. A memory location (00:0000h-00:FFFFh) addressed indirectly through word register (WR0- WR30) + 16-bit signed (two's complement) displacement value Word register index: j, jd, js= 0-30	J	
DRk DRkd DRks @DRk @DRk +dis16 k, kd, ks	Dword register DR0, DR4,, DR28, DR56, DR60 of the currently selected register file Destination register Source register A memory location (00:0000h-FF:FFFFh) addressed indirectly through dword register DR0- DR28, DR56 and DR60, is the target address for jump instruction A memory location (00:0000h-FF:FFFFh) addressed indirectly through dword register (DR0- DR28, DR56, DR60) + 16-bit (two's complement) signed displacement value Dword register index: k, kd, ks= 0, 4, 8, 28, 56, 60	J	



7.2 Size and Execution Time for Instruction Families

Add Subtract Add with Carry Subtract with Borrow		$ \begin{array}{llllllllllllllllllllllllllllllllllll$					
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Commente	Bina	ry Mode	Source	e Mode	
Minemonic	<uest>, <src>(-)</src></uest>	Comments	Bytes	States	Bytes	States	
	A, Rn	Register to ACC	1	1	2	2	
ADD	A, dir8	Direct address to ACC	2	1 ⁽²⁾	2	1 ⁽²⁾	
ADD	A, @Ri	Indirect address to ACC	1	2	2	3	
	A, #data	Immediate data to ACC	2	1	2	1	
	Rmd, Rms	Byte register to/from byte register	3	2	2	1	
	WRjd, WRjs	Word register to/from word register	3	3	2	2	
	DRkd, DRks	Dword register to/from dword register	3	5	2	4	
	Rm, #data	Immediate 8-bit data to/from byte register	4	3	3	2	
	WRj, #data16	mmediate 16-bit data to/from word register		4	4	3	
	DRk, #0data16	6-bit unsigned immediate data to/from dword register		6	4	5	
ADD / SUB	Rm, dir8	Direct address (on-chip RAM or SFR) to/from byte reg	gister 4	3(2)	3	2 ⁽²⁾	
	WRj, dir8	Direct address (on-chip RAM or SFR) to/from word reg	gister 4	4	3	3	
	Rm, dir16	Direct address (64K) to/from byte register	5	3(3)	4	2 ⁽³⁾	
	WRj, dir16	Direct address (64K) to/from word register	5	4 ⁽⁴⁾	4	3(4)	
	Rm, @WRj	Indirect address (64K) to/from byte register	4	3(3)	3	2 ⁽³⁾	
	Rm, @DRk	Indirect address (16M) to/from byte register	4	4 ⁽³⁾	3	3(3)	
	A, Rn	Register to/from ACC with carry	1	1	2	2	
ADDC / SUBB	A, dir8	Direct address (on-chip RAM or SFR) to/from ACC v carry	with 2	1(2)	2	1(2)	
	A, @Ri	Indirect address to/from ACC with carry	1	2	2	3	
	A, #data	Immediate data to/from ACC with carry	2	1	2	1	

Table 20. Summary of Add and Subtract Instructions

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

3. If this instruction addresses external memory location, add N+2 to the number of states (N: number of wait states).

4. If this instruction addresses external memory location, add 2(N+2) to the number of states (N: number of wait states).

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Increment Increment Decrement Decrement		$\begin{array}{llllllllllllllllllllllllllllllllllll$					
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comments			Mode		Mode
			Bytes	States	Bytes	States	
	А	ACC by 1		1	1	1	1
INC	Rn	Register by 1		1	1	2	2
DEC	dir8	Direct address (on-chip RAM or SFR) by 1		2	2 ⁽²⁾	2	2 ⁽²⁾
	@Ri	Indirect address by 1		1	3	2	4
INC	Rm, #short	Byte register by 1, 2, or 4		3	2	2	1
DEC	WRj, #short	Word register by 1, 2, or 4		3	2	2	1
INC	DRk, #short	Double word register by 1, 2, or 4		3	4	2	3
DEC	DRk, #short	Double word register by 1, 2, or 4		3	5	2	4
INC	DPTR	Data pointer by 1		1	1	1	1

Table 21. Summary of Increment and Decrement Instructions

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. If this instruction addresses an I/O Port (Px, x = 0-3), add 2 to the number of states. Add 3 if it addresses a Peripheral SFR.

Table 22. Summary of Compare Instructions

Compare		CMP <dest>, <src> dest opnd - sr</src></dest>	re opnd			
N/	<dest>, <src>⁽²⁾</src></dest>	Comments		Binary Mode		e Mode
Mnemonic	<uest>, <src></src></uest>		Bytes	States	Bytes	States
	Rmd, Rms	Register with register	3	2	2	1
	WRjd, WRjs	Word register with word register	3	3	2	2
	DRkd, DRks	Dword register with dword register	3	5	2	4
	Rm, #data	Register with immediate data	4	3	3	2
	WRj, #data16	Word register with immediate 16-bit data	5	4	4	3
	DRk, #0data16	Dword register with zero-extended 16-bit immediate data	5	6	4	5
CMP	DRk, #1data16	Dword register with one-extended 16-bit immediate data	5	6	4	5
	Rm, dir8	Direct address (on-chip RAM or SFR) with byte register	4	3(1)	3	2 ⁽¹⁾
	WRj, dir8	Direct address (on-chip RAM or SFR) with word register	4	4	3	3
	Rm, dir16	Direct address (64K) with byte register	5	3 ⁽²⁾	4	2 ⁽²⁾
	WRj, dir16	Direct address (64K) with word register	5	4 ⁽³⁾	4	3(3)
	Rm, @WRj	Indirect address (64K) with byte register	4	3(2)	3	2 ⁽²⁾
	Rm, @DRk	Indirect address (16M) with byte register	4	4 ⁽²⁾	3	3(2)

Notes:

1. If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

2. If this instruction addresses external memory location, add N+2 to the number of states (N: number of wait states).

3. If this instruction addresses external memory location, add 2(N+2) to the number of states (N: number of wait states).



		Table 23. Summary of Logical Instruction	Table 23. Summary of Logical Instructions (1/2)					
Logical AND ⁽¹⁾ Logical OR ⁽¹⁾ Logical Exclusi Clear ⁽¹⁾ Complement ⁽¹⁾ Rotate Left Rotate Left Car Rotate Right Rotate Right Ca	ve OR ⁽¹⁾ ry	$\begin{array}{cccc} \text{ORL} & <\text{dest} >, <\text{src>} & \text{dest} \text{ ond} \\ \text{XRL} & <\text{dest>}, <\text{src>} & \text{dest} \text{ opnd} \\ \text{CLR A} & (A) \leftarrow 0 \\ \text{CPL A} & (A) \leftarrow \emptyset \\ \text{RL A} & (A)_{n+1} \leftarrow \\ & (A)_0 \leftarrow (0) \\ \text{RLC A} & (A)_{n+1} \leftarrow \\ & (CY) \leftarrow 0 \\ & (A)_0 \leftarrow (0) \\ \text{RR A} & (A)_{n-1} \leftarrow \\ & (A)_7 \leftarrow (0) \\ \end{array}$	$\begin{array}{l} (A)_{n}, \ n=06\\ A)_{7}\\ (A)_{n}, \ n=06\\ (A)_{7}\\ CY)\\ (A)_{n}, \ n=71\\ A)_{0}\\ (A)_{n}, \ n=71\\ (A)_{0}\end{array}$	ς src opnd				
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comments	Binary	Mode	Source	Mode		
Winemonie		Comments	Bytes	States	Bytes	States		
	A, Rn	register to ACC	1	1	2	2		
	A, dir8	Direct address (on-chip RAM or SFR) to ACC	2	1 ⁽³⁾	2	1 ⁽³⁾		
	A, @Ri	Indirect address to ACC	1	2	2	3		
	A, #data	Immediate data to ACC	2	1	2	1		
	dir8, A	ACC to direct address	2	2 ⁽⁴⁾	2	2 ⁽⁴⁾		
	dir8, #data	Immediate 8-bit data to direct address	3	3 ⁽⁴⁾	3	3 ⁽⁴⁾		
	Rmd, Rms	Byte register to byte register	3	2	2	1		
ANL ORL	WRjd, WRjs	Word register to word register	3	3	2	2		
XRL	Rm, #data	Immediate 8-bit data to byte register	4	3	3	2		
	WRj, #data16	Immediate 16-bit data to word register	5	4	4	3		
	Rm, dir8	Direct address (on-chip RAM or SFR) to byte register	4	3 ⁽³⁾	3	2 ⁽³⁾		
	WRj, dir8	Direct address (on-chip RAM or SFR) to word register	r 4	4	3	3		
	Rm, dir16	Direct address (64K) to byte register	5	3 ⁽⁵⁾	4	2 ⁽⁵⁾		
	WRj, dir16	Direct address (64K) to word register	5	4 ⁽⁶⁾	4	3 ⁽⁶⁾		
	Rm, @WRj	Indirect address (64K) to byte register	4	3 ⁽⁵⁾	3	2 ⁽⁵⁾		
	Rm, @DRk	Indirect address (16M) to byte register	4	4 ⁽⁵⁾	3	3 ⁽⁵⁾		
CLR	А	Clear ACC	1	1	1	1		
CPL	А	Complement ACC	1	1	1	1		
RL	А	Rotate ACC left	1	1	1	1		
RLC	А	Rotate ACC left through CY	1	1	1	1		
RR	А	Rotate ACC right	1	1	1	1		
RRC	А	Rotate ACC right through CY	1	1	1	1		

Notes:

1. Logical instructions that affect a bit are in Table 29.

- 2. A shaded cell denotes an instruction in the C51 Architecture.
- 3. If this instruction addresses an I/O Port (Px, x = 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.
- 4. If this instruction addresses an I/O Port (Px, x= 0-3), add 2 to the number of states. Add 3 if it addresses a Peripheral SFR.
- 5. If this instruction addresses external memory location, add N+2 to the number of states (N: number of wait states).

6. If this instruction addresses external memory location, add 2(N+2) to the number of states (N: number of wait states).

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		Table 24. Summary of Logical In	structions (2	2/2)				
Shift Left Logic	cal	SLL <dest></dest>	$\langle \text{dest} \rangle_0 \leftarrow 0$ $\langle \text{dest} \rangle_{n+1} \leftarrow \langle \text{dest} \rangle_n, n= 0msb-1$ $(CY) \leftarrow \langle \text{dest} \rangle_{msb}$					
Shift Right Arithmetic		SRA <dest></dest>	$\langle \text{dest} \rangle_{\text{msb}} \leftarrow \langle \text{dest} \rangle_{\text{msb}}$ $\langle \text{dest} \rangle_{\text{n-1}} \leftarrow \langle \text{dest} \rangle_{\text{n}}, \text{ n= msb1}$ $(\text{CY}) \leftarrow \langle \text{dest} \rangle_{0}$					
Shift Right Log	ical	SRL <dest></dest>	$\langle \text{dest} \rangle_{\text{msb}} \leftarrow 0$ $\langle \text{dest} \rangle_{\text{n-1}} \leftarrow \langle \text{dest} \rangle_{\text{n}}, \text{ n= msb1}$ $(\text{CY}) \leftarrow \langle \text{dest} \rangle_{0}$					
Swap		SWAP A	A _{3:0} A _{7:4}					
M	<dest>, <src>⁽¹⁾</src></dest>	Comments		Binary	Mode	Source	e Mode	
Mnemonic	<uest>, <src></src></uest>			Bytes	States	Bytes	States	
CI I	Rm	Shift byte register left through the MSB		3	2	2	1	
SLL	WRj	Shift word register left through the MSB		3	2	2	1	
SRA	Rm	Shift byte register right		3	2	2	1	
SKA	WRj	Shift word register right		3	2	2	1	
SRL	Rm	Shift byte register left		3	2	2	1	
SKL	WRj	Shift word register left		3	2	2	1	
SWAP	А	Swap nibbles within ACC		1	2	1	2	

Note:

1. A shaded cell denotes an instruction in the C51 Architecture.

Table 25. Summary of Multiply, Divide and Decimal-adjust Instructions

Multiply		MUL AB	$(B:A) \leftarrow (A)$	×(B)		$(B:A) \leftarrow (A) \!\times\! (B)$				
		MUL <dest>, <src></src></dest>	extended dest opnd \leftarrow dest opnd \times src opnd							
Divide		DIV AB	$(A) \leftarrow Quotion$	ent ((A)/(B))					
			$(B) \leftarrow Remai$,	. ,,					
Divide		DIV <dest>, <src></src></dest>	ext. dest opnd high \leftarrow Quotient (dest opnd / src opnd				· ·			
D · 1 · 1 · .	1.00		ext. dest opnd low \leftarrow Remainder (dest opnd / src opnd				src opnd)			
Decimal-adjust		DA A		IF $[[(A)_{3:0} > 9] \lor [(AC)= 1]]$ THEN $(A)_{3:0} \leftarrow (A)_{3:0} + 6$!affects CY;						
for Addition (B	CD)		IF $[[(A)_{7\cdot 4} >$	510	. 510		,			
				$(A)_{7:4} \leftarrow (A)_{7:4}$						
M	<dest>, <src>⁽¹⁾</src></dest>	() Comments -		Binary Mode		Mode	Source Mode			
Mnemonic	<uest>, <src></src></uest>			Bytes	States	Bytes	States			
	AB	Multiply A and B		1	5	1	5			
MUL	Rmd, Rms	Multiply byte register and byte register		3	6	2	5			
	WRjd, WRjs	Multiply word register and word register		3	12	2	11			
	AB	Divide A and B		1	10	1	10			
DIV	Rmd, Rms	Divide byte register and byte register		3	11	2	10			
	WRjd, WRjs	Divide word register and word register		3	21	2	20			
DA	А	Decimal adjust ACC		1	1	1	1			

Note:

1. A shaded cell denotes an instruction in the C51 Architecture.



$ \begin{array}{ c c c c c c } \hline Move to High word & MOVH , & dest opnd_{31:16} \leftarrow src opnd \\ \hline Move with Sign extension & MOVS , & dest opnd \leftarrow src opnd with sign exten \\ \hline Move with Zero extension & MOVZ , & dest opnd \leftarrow src opnd with zero exten \\ \hline Move Code & MOVC A, & (A) \leftarrow src opnd \\ \hline Move eXtended & MOVX , & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, & dest opnd \leftarrow src opnd \\ \hline Move A, $							
Mnemonic	<dest>, <src>⁽²⁾</src></dest>	rc> ⁽²⁾ Comments	Binary	Mode	Source	e Mode	
		Comments		lytes	States	Bytes	States
MOVH	DRk, #data16	16-bit immediate data into upper word of dword register	ster	5	3	4	2
MOVS	WRj, Rm	Byte register to word register with sign extension		3	2	2	1
MOVZ	WRj, Rm	Byte register to word register with zeros extension		3	2	2	1
MOVC	A, @A +DPTR	Code byte relative to DPTR to ACC		1	6 ⁽³⁾	1	6 ⁽³⁾
MOVC	A, @A +PC	Code byte relative to PC to ACC		1	6 ⁽³⁾	1	6 ⁽³⁾
	A, @Ri	Extended memory (8-bit address) to ACC ⁽²⁾		1	4	1	5
MONA	A, @DPTR	Extended memory (16-bit address) to ACC ⁽²⁾		1	3 ⁽⁴⁾	1	3(4)
MOVX	@Ri, A	ACC to extended memory (8-bit address) ⁽²⁾		1	4	1	4
	@DPTR, A	ACC to extended memory (16-bit address) ⁽²⁾		1	4 ⁽³⁾	1	4 ⁽³⁾

Table 26. Summary of Move Instructions (1/3)

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. Extended memory addressed is in the region specified by DPXL (reset value= 01h).

3. If this instruction addresses external memory location, add N+1 to the number of states (N: number of wait states).

4. If this instruction addresses external memory location, add N+2 to the number of states (N: number of wait states).

Table 27. Summary of Move Instructions (2/3)

Move ⁽¹⁾		$\text{MOV} <\!\!\text{dest}\!\!>, <\!\!\text{src}\!\!> \qquad \qquad \text{dest opnd} \leftarrow$	src opnd			
Mnemonic	<dest>, <src>⁽²⁾</src></dest>	Comments	Binary Mode		Source Mode	
Millemonic	<uest>, <src></src></uest>	Comments	Bytes	States	Bytes	States
	A, Rn	Register to ACC	1	1	2	2
	A, dir8	Direct address (on-chip RAM or SFR) to ACC	2	1 ⁽³⁾	2	1 ⁽³⁾
	A, @Ri	Indirect address to ACC	1	2	2	3
	A, #data	Immediate data to ACC	2	1	2	1
	Rn, A	ACC to register	1	1	2	2
	Rn, dir8	Direct address (on-chip RAM or SFR) to register	2	1 ⁽³⁾	3	2 ⁽³⁾
	Rn, #data	Immediate data to register	2	1	3	2
MOV	dir8, A	ACC to direct address (on-chip RAM or SFR)	2	2 ⁽³⁾	2	2 ⁽³⁾
	dir8, Rn	Register to direct address (on-chip RAM or SFR)	2	2 ⁽³⁾	3	3 ⁽³⁾
	dir8, dir8	Direct address to direct address (on-chip RAM or SFR)	3	3(4)	3	3(4)
	dir8, @Ri	Indirect address to direct address (on-chip RAM or SFR)	2	3(3)	3	4 ⁽³⁾
	dir8, #data	Immediate data to direct address (on-chip RAM or SFR)	3	3 ⁽³⁾	3	3 ⁽³⁾
	@Ri, A	ACC to indirect address	1	3	2	4
	@Ri, dir8	Direct address (on-chip RAM or SFR) to indirect address	2	3(3)	3	4 ⁽³⁾
	@Ri, #data	Immediate data to indirect address	2	3	3	4
	DPTR, #data16	Load Data Pointer with a 16-bit constant	3	2	3	2

Notes:

1. Instructions that move bits are in Table 29.

2. Move instructions from the C51 Architecture.

3. If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

4. Apply note 3 for each dir8 operand.

Move ⁽¹⁾		$MOV \ \ \ \ dest \ \ opnd \ \leftarrow$	src opnd			
			Binary	Mode	Source Mode	
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comments	Bytes	States	Bytes	States
	Rmd, Rms	Byte register to byte register	3	2	2	1
	WRjd, WRjs	Word register to word register	3	2	2	1
	DRkd, DRks	Dword register to dword register	3	3	2	2
	Rm, #data	Immediate 8-bit data to byte register	4	3	3	2
	WRj, #data16	Immediate 16-bit data to word register	5	3	4	2
	DRk, #0data16	zero-ext 16bit immediate data to dword register	5	5	4	4
	DRk, #1data16	one-ext 16bit immediate data to dword register	5	5	4	4
	Rm, dir8	Direct address (on-chip RAM or SFR) to byte register	4	3(3)	3	2 ⁽³⁾
	WRj, dir8	Direct address (on-chip RAM or SFR) to word register	4	4	3	3
	DRk, dir8	Direct address (on-chip RAM or SFR) to dword register	4	6	3	5
	Rm, dir16	Direct address (64K) to byte register	5	3(4)	4	2 ⁽⁴⁾
	WRj, dir16	Direct address (64K) to word register	5	4 ⁽⁵⁾	4	3(5)
	DRk, dir16	Direct address (64K) to dword register	5	6 ⁽⁶⁾	4	5 ⁽⁶⁾
	Rm, @WRj	Indirect address (64K) to byte register	4	3(4)	3	2 ⁽⁴⁾
	Rm, @DRk	Indirect address (16M) to byte register	4	4 ⁽⁴⁾	3	3(4)
	WRjd, @WRjs	Indirect address (64K) to word register	4	4 ⁽⁵⁾	3	3(5)
	WRj, @DRk	Indirect address (16M) to word register	4	5 ⁽⁵⁾	3	4 ⁽⁵⁾
MOV	dir8, Rm	Byte register to direct address (on-chip RAM or SFR)	4	4 ⁽³⁾	3	3 ⁽³⁾
	dir8, WRj	Word register to direct address (on-chip RAM or SFR)	4	5	3	4
	dir8, DRk	Dword register to direct address (on-chip RAM or SFR)	4	7	3	6
	dir16, Rm	Byte register to direct address (64K)	5	4 ⁽⁴⁾	4	3(4)
	dir16, WRj	Word register to direct address (64K)	5	5 ⁽⁵⁾	4	4 ⁽⁵⁾
	dir16, DRk	Dword register to direct address (64K)	5	7 ⁽⁶⁾	4	6(6)
	@WRj, Rm	Byte register to indirect address (64K)	4	4 ⁽⁴⁾	3	3(4)
	@DRk, Rm	Byte register to indirect address (16M)	4	5 ⁽⁴⁾	3	4 ⁽⁴⁾
	@WRjd, WRjs	Word register to indirect address (64K)	4	5(5)	3	4 ⁽⁵⁾
	@DRk, WRj	Word register to indirect address (16M)	4	6 ⁽⁵⁾	3	5 ⁽⁵⁾
	Rm, @WRj +dis16	Indirect with 16-bit displacement (64K) to byte register	5	6(4)	4	5(4)
	WRj, @WRj +dis16	Indirect with 16-bit displacement (64K) to word register	5	7 ⁽⁵⁾	4	6 ⁽⁵⁾
	Rm, @DRk +dis24	Indirect with 16-bit displacement (16M) to byte register	5	7 ⁽⁴⁾	4	6(4)
	WRj, @WRj +dis24	Indirect with 16-bit displacement (16M) to word register	5	8(5)	4	7 ⁽⁵⁾
	@WRj +dis16, Rm	Byte register to indirect with 16-bit displacement (64K)	5	6 ⁽⁴⁾	4	5(4)
	@WRj +dis16, WRj		5	7 ⁽⁵⁾	4	6 ⁽⁵⁾
	@DRk +dis24, Rm	Byte register to indirect with 16-bit displacement (16M)	5	7 ⁽⁴⁾	4	6(4)
	@DRk +dis24, WRj		5	8(5)	4	7 ⁽⁵⁾

Table 28. Summary of Move Instructions (3/3)

Notes:

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^{1.} Instructions that move bits are in Table 29.

^{2.} Move instructions unique to the C251 Architecture.

^{3.} If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

^{4.} If this instruction addresses external memory location, add N+2 to the number of states (N: number of wait states).

^{5.} If this instruction addresses external memory location, add 2(N+1) to the number of states (N: number of wait states).

^{6.} If this instruction addresses external memory location, add 4(N+2) to the number of states (N: number of wait states).



Clear Bit		CLR <dest></dest>	dest opnd \leftarrow	0			
Set Bit		SETB <dest></dest>	dest opnd \leftarrow				
Complement Bi	it	CPL <dest></dest>	dest opnd \leftarrow	Ø bit			
AND Carry wit		ANL CY, <src></src>	$(CY) \leftarrow (CY) \land src opnd$				
•	th Complement of Bit		$(CY) \leftarrow (CY)$				
OR Carry with		ORL CY, <src></src>	$(CY) \leftarrow (CY)$	· 1			
•	Complement of Bit	ORL CY, / <src></src>	$(CY) \leftarrow (CY)$		opnd		
Move Bit to Ca Move Bit from	J	MOV CY, <src> MOV <dest>, CY</dest></src>	$(CY) \leftarrow src odd dest opnd \leftarrow$				
Nove Bit nom							
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Commente		Binary	Mode	Source	e Mode
Minemonic	<dest>, <src></src></dest>	Comments		Bytes	States	Bytes	States
	СҮ	Clear carry		1	1	1	1
CLR	bit51	Clear direct bit		2	2 ⁽³⁾	2	2 ⁽³⁾
	bit	Clear direct bit		4	4 ⁽³⁾	3	3 ⁽³⁾
	CY	Set carry		1	1	1	1
-	bit51	Set direct bit		2	2 ⁽³⁾	2	2 ⁽³⁾
	bit	Set direct bit		4	4 ⁽³⁾	3	3 ⁽³⁾
	CY	Complement carry		1	1	1	1
CPL	bit51	Complement direct bit		2	2 ⁽³⁾	2	2 ⁽³⁾
	bit	Complement direct bit		4	4 ⁽³⁾	3	3 ⁽³⁾
	CY, bit51	And direct bit to carry		2	1 ⁽²⁾	2	1 ⁽²⁾
ANL	CY, bit	And direct bit to carry		4	3 ⁽²⁾	3	2 ⁽²⁾
	CY, /bit51	And complemented direct bit to carry		2	1 ⁽²⁾	2	1 ⁽²⁾
	CY, /bit	And complemented direct bit to carry		4	3(2)	3	2 ⁽²⁾
	CY, bit51	Or direct bit to carry		2	1 ⁽²⁾	2	1 ⁽²⁾
ORL	CY, bit	Or direct bit to carry		4	3(2)	3	2 ⁽²⁾
UNL	CY, /bit51	Or complemented direct bit to carry		2	1 ⁽²⁾	2	1 ⁽²⁾
	CY, /bit	Or complemented direct bit to carry		4	3 ⁽²⁾	3	2 ⁽²⁾
	CY, bit51	Move direct bit to carry		2	1 ⁽²⁾	2	1 ⁽²⁾
MOV	CY, bit	Move direct bit to carry		4	3 ⁽²⁾	3	2 ⁽²⁾
1010 4	bit51, CY	Move carry to direct bit		2	2 ⁽³⁾	2	2 ⁽³⁾
	bit, CY	Move carry to direct bit		4	4 ⁽³⁾	3	3 ⁽³⁾

Table 29. Summary of Bit Instructions

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. If this instruction addresses an I/O Port (Px, x = 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

3. If this instruction addresses an I/O Port (Px, x= 0-3), add 2 to the number of states. Add 3 if it addresses a Peripheral SFR.

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Exchange bytesXCH A, $\langle src \rangle$ (A) \leftrightarrow src opnd							
Exchange Digit		XCHD A, <src></src>	$(A)_{3:0} \leftrightarrow src$				
Push		$PUSH < src> (SP) \leftarrow (SP) +1; ((SP)) \leftarrow src opnd;$				ıd;	
			$(SP) \leftarrow (SP)$				
Pop		POP <dest></dest>	$(SP) \leftarrow (SP)$		-		
	1		dest opnd \leftarrow	((SP)); (SI	$(SP) \leftarrow (SP)$	-1	
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Commente		Binary	Mode	Source Mode	
Minemonic	<uest>, <src></src></uest>	Comments		Bytes	States	Bytes	States
	A, Rn	ACC and register		1	3	2	4
ХСН	A, dir8	ACC and direct address (on-chip RAM or SFR)		2	3(3)	2	3(3)
A, @Ri A		ACC and indirect address		1	4	2	5
XCHD	A, @Ri	ACC low nibble and indirect address (256 bytes)		1	4	2	5
	dir8	Push direct address onto stack		2	2 ⁽²⁾	2	2 ⁽²⁾
	#data	Push immediate data onto stack		4	4	3	3
PUSH	#data16	Push 16-bit immediate data onto stack		5	5	4	5
rusn	Rm	Push byte register onto stack		3	4	2	3
	WRj	Push word register onto stack		3	5	2	4
	DRk	Push double word register onto stack		3	9	2	8
	dir8	Pop direct address (on-chip RAM or SFR) from stack		2	3(2)	2	3(2)
DOD	Rm	Pop byte register from stack		3	3	2	2
POP	WRj	Pop word register from stack		3	5	2	4
	DRk	Pop double word register from stack		3	9	2	8

Table 30. Summary of Exchange, Push and Pop Instructions

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

3. If this instruction addresses an I/O Port (Px, x = 0-3), add 2 to the number of states. Add 3 if it addresses a Peripheral SFR.

Table 31. Summary of Conditional Jump Instructions (1/2)

Jump conditional on status Jcc rel			$(PC) \leftarrow (PC) + size (instr);$ IF [cc] THEN $(PC) \leftarrow (PC) + rel$			
Marania	<dest>, <src>⁽¹⁾</src></dest>		Binary Mode		Source Mode	
Mnemonic	onic <dest>, <src>⁽¹⁾ Comments</src></dest>	Bytes	States	Bytes	States	
JC	rel	Jump if carry	2	1/4 ⁽³⁾	2	1/4 ⁽³⁾
JNC	rel	Jump if not carry	2	1/4 ⁽³⁾	2	1/4 ⁽³⁾
JE	rel	Jump if equal	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JNE	rel	Jump if not equal	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JG	rel	Jump if greater than	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JLE	rel	Jump if less than, or equal	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JSL	rel	Jump if less than (signed)	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JSLE	rel	Jump if less than, or equal (signed)	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JSG	rel	Jump if greater than (signed)	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾
JSGE	rel	Jump if greater than or equal (signed)	3	2/5 ⁽³⁾	2	1/4 ⁽³⁾

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. States are given as jump not-taken/taken.

3. In internal execution only, add 1 to the number of states of the 'jump taken' if the destination address is internal and odd.

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	Table 32. Summary of Conditional Jump Instructions (2/2)						
Jump if bit		JB <src>, rel</src>	$(PC) \leftarrow (PC) + size (instr);$				
-			IF [src opnd= 1] THEN (PC) \leftarrow (PC) + rel				
Jump if not bit		JNB <src>, rel</src>	$(PC) \leftarrow (PC) + size (instr);$				
			IF [src opnd= 0] THEN (PC) \leftarrow (PC) + rel				
Jump if bit and	clear	JBC <dest>, rel</dest>	$(PC) \leftarrow (PC) + size (instr);$				
			IF [dest opnd= 1] THEN				
			dest opnd $\leftarrow 0$				
			$(PC) \leftarrow (PC) + rel$				
Jump if accumu	lator is zero	JZ rel	$(PC) \leftarrow (PC) + size (instr);$				
			IF $[(A)= 0]$ THEN $(PC) \leftarrow (PC) + rel$				
Jump if accumu	lator is not zero	JNZ rel	$(PC) \leftarrow (PC) + size (instr);$				
			IF $[(A) \neq 0]$ THEN (PC) \leftarrow (PC) + rel				
Compare and ju	mp if not equal	CJNE <src1>, <src2>, rel</src2></src1>	$(PC) \leftarrow (PC) + size (instr);$				
			IF [src opnd1 < src opnd2] THEN (CY) \leftarrow 1				
			IF [src opnd1 \geq src opnd2] THEN (CY) $\leftarrow 0$				
			IF [src opnd1 \neq src opnd2] THEN (PC) \leftarrow (PC) + rel				
Decrement and jump if not zero DJNZ <dest>,</dest>		DJNZ <dest>, rel</dest>	$(PC) \leftarrow (PC) + size (instr); dest opnd \leftarrow dest opnd -1;$				
			IF $[\phi(Z)]$ THEN $(PC) \leftarrow (PC) + rel$				
Maaaata	(1)	Comment	Binary Mode ⁽²⁾ Source Mode ⁽²⁾				
Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comment	IS Deuton Staten Deuton Staten				

Mnemonic	<dest>, <src>⁽¹⁾ Comments</src></dest>		Binary	Binary Mode ⁽²⁾		Mode ⁽²⁾
winemonic	<uest>, <src></src></uest>	Comments	Bytes	States	Bytes	States
JB	bit51, rel	Jump if direct bit is set	3	2/5 ⁽³⁾⁽⁶⁾	3	2/5 ⁽³⁾⁽⁶⁾
JP	bit, rel	Jump if direct bit of 8-bit address location is set	5	4/7 ⁽³⁾⁽⁶⁾	4	3/6 ⁽³⁾⁽⁶⁾
JNB	bit51, rel	Jump if direct bit is not set	3	2/5 ⁽³⁾⁽⁶⁾	3	2/5 ⁽³⁾⁽⁶⁾
JIND	bit, rel	Jump if direct bit of 8-bit address location is not set	5	4/7 ⁽³⁾⁽⁶⁾	4	3/6 ⁽³⁾
JBC	bit51, rel	Jump if direct bit is set & clear bit		4/7 ⁽⁵⁾⁽⁶⁾	3	4/7 ⁽⁵⁾⁽⁶⁾
bit, rel	bit, rel	Jump if direct bit of 8-bit address location is set and clear	5	7/10 ⁽⁵⁾⁽⁶⁾	4	6/9 ⁽⁵⁾⁽⁶⁾
JZ	rel	Jump if ACC is zero		2/5 ⁽⁶⁾	2	2/5 ⁽⁶⁾
JNZ	rel	Jump if ACC is not zero	2	2/5 ⁽⁶⁾	2	2/5 ⁽⁶⁾
	A, dir8, rel	Compare direct address to ACC and jump if not equal	3	2/5 ⁽³⁾⁽⁶⁾	3	2/5 ⁽³⁾⁽⁶⁾
CJNE	A, #data, rel	Compare immediate to ACC and jump if not equal	3	2/5 ⁽⁶⁾	3	2/5 ⁽⁶⁾
CINE	Rn, #data, rel	Compare immediate to register and jump if not equal	3	2/5 ⁽⁶⁾	4	3/6 ⁽⁶⁾
	@Ri, #data, rel	Compare immediate to indirect and jump if not equal	3	3/6 ⁽⁶⁾	4	4/7 ⁽⁶⁾
DJNZ	Rn, rel	Decrement register and jump if not zero	2	2/5 ⁽⁶⁾	3	3/6 ⁽⁶⁾
DINZ	dir8, rel	Decrement direct address and jump if not zero	3	3/6 ⁽⁴⁾⁽⁶⁾	3	3/6 ⁽⁴⁾⁽⁶⁾

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. States are given as jump not-taken/taken.

3. If this instruction addresses an I/O Port (Px, x= 0-3), add 1 to the number of states. Add 2 if it addresses a Peripheral SFR.

4. If this instruction addresses an I/O Port (Px, x= 0-3), add 2 to the number of states. Add 3 if it addresses a Peripheral SFR.

5. If this instruction addresses an I/O Port (Px, x= 0-3), add 3 to the number of states. Add 5 if it addresses a Peripheral SFR.

6. In internal execution only, add 1 to the number of states of the 'jump taken' if the destination address is internal and odd.

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Absolute jump	AJMP <src></src>	$(PC) \leftarrow (PC) +2; (PC)_{10:0} \leftarrow src opnd$
Extended jump	EJMP <src></src>	$(PC) \leftarrow (PC) + size (instr); (PC)_{23:0} \leftarrow src opnd$
Long jump	LJMP <src></src>	$(PC) \leftarrow (PC) + \text{size (instr)}; (PC)_{15:0} \leftarrow \text{src opnd}$
Short jump	SJMP rel	$(PC) \leftarrow (PC) +2; (PC) \leftarrow (PC) +rel$
Jump indirect	JMP @A +DPTR	$(PC)_{23:16} \leftarrow FFh; (PC)_{15:0} \leftarrow (A) + (DPTR)$
No operation	NOP	$(PC) \leftarrow (PC) + 1$

Table 33. Summary of unconditional Jump Instructions

Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comments	Binary Mode		Source Mode	
			Bytes	States	Bytes	States
AJMP	addr11	Absolute jump	2	3 ⁽²⁾⁽³⁾	2	3 ⁽²⁾⁽³⁾
EMD	addr24	Extended jump	5	6 ⁽²⁾⁽⁴⁾	4	5 ⁽²⁾⁽⁴⁾
EJMP @DF	@DRk	Extended jump (indirect)	3	7 ⁽²⁾⁽⁴⁾	2	6 ⁽²⁾⁽⁴⁾
@WRj		Long jump (indirect)	3	6 ⁽²⁾⁽⁴⁾	2	5 ⁽²⁾⁽⁴⁾
LJMP	addr16	Long jump (direct address)	3	5 ⁽²⁾⁽⁴⁾	3	5 ⁽²⁾⁽⁴⁾
SJMP	rel	Short jump (relative address)	2	4 ⁽²⁾⁽⁴⁾	2	4 ⁽²⁾⁽⁴⁾
JMP	@A +DPTR	Jump indirect relative to the DPTR	1	5 ⁽²⁾⁽⁴⁾	1	5 ⁽²⁾⁽⁴⁾
NOP		No operation (Jump never)	1	1	1	1
		•				

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. In internal execution only, add 1 to the number of states if the destination address is internal and odd.

3. Add 2 to the number of states if the destination address is external.

4. Add 3 to the number of states if the destination address is external.

Table 34. Summary of Call and Return Instructions

Absolute call	ACALL <src></src>	$(PC) \leftarrow (PC) +2$; push $(PC)_{15:0}$;
		$(PC)_{10:0} \leftarrow src opnd$
Extended call	ECALL <src></src>	$(PC) \leftarrow (PC) + size (instr); push (PC)_{23:0};$
		$(PC)_{23:0} \leftarrow src opnd$
Long call	LCALL <src></src>	$(PC) \leftarrow (PC) + size (instr); push (PC)_{15:0};$
		$(PC)_{15:0} \leftarrow src opnd$
Return from subroutine	RET	pop (PC) _{15:0}
Extended return from subroutine	ERET	pop $(PC)_{23:0}$
Return from interrupt	RETI	IF [INTR= 0] THEN pop $(PC)_{15:0}$
		IF [INTR= 1] THEN pop $(PC)_{23:0}$; pop $(PSW1)$
Trap interrupt	TRAP	$(PC) \leftarrow (PC) + size (instr);$
		IF [INTR= 0] THEN push (PC) _{15:0}
		IF [INTR= 1] THEN push (PSW1); push (PC) _{23:0}

Mnemonic	<dest>, <src>⁽¹⁾</src></dest>	Comments	Binary Mode		Source Mode	
wittemonic	<uest>, <src></src></uest>		Bytes	States	Bytes	States
ACALL	addr11	Absolute subroutine call	2	9 ⁽²⁾⁽³⁾	2	9 ⁽²⁾⁽³⁾
ECALI	@DRk	Extended subroutine call (indirect)	3	14 ⁽²⁾⁽³⁾	2	13 ⁽²⁾⁽³⁾
ECALL addr24		Extended subroutine call	5	14 ⁽²⁾⁽³⁾	4	13 ⁽²⁾⁽³⁾
@WRj		Long subroutine call (indirect)	3	10 ⁽²⁾⁽³⁾	2	9 ⁽²⁾⁽³⁾
LCALL	addr16	Long subroutine call	3	9 ⁽²⁾⁽³⁾	3	9 ⁽²⁾⁽³⁾
RET		Return from subroutine	1	7 ⁽²⁾	1	7 ⁽²⁾
ERET		Extended subroutine return	3	9 ⁽²⁾	2	8 ⁽²⁾
RETI		Return from interrupt	1	7 ⁽²⁾⁽⁴⁾	1	7 ⁽²⁾⁽⁴⁾
TRAP		Jump to the trap interrupt vector	2	12 ⁽⁴⁾	1	11 ⁽⁴⁾

Notes:

1. A shaded cell denotes an instruction in the C51 Architecture.

2. In internal execution only, add 1 to the number of states if the destination/return address is internal and odd.

3. Add 2 to the number of states if the destination address is external.

4. Add 5 to the number of states if INTR= 1.



8. Programming and Verifying Non-Volatile Memory

8.1 Internal Features

The internal non-volatile memory of the TSC80251G2D derivatives contains five different areas:

- Code Memory
- Configuration Bytes
- Lock Bits
- Encryption Array
- Signature Bytes

8.1.1 EPROM/OTPROM Devices

All the internal non-volatile memory but the Signature Bytes of the TSC87251G2D products is made of EPROM cells. The Signature Bytes of the TSC87251G2D products are made of Mask ROM.

The TSC87251G2D products are programmed and verified in the same manner as TEMIC's TSC87251G1A, using a SINGLE-PULSE algorithm, which programs at V_{PP} = 12.75V using only one 100 µs pulse per byte. This results in a programming time of less than 10 seconds for the 32 Kbytes on-chip code memory.

The EPROM of the TSC87251G2D products in Window package is erasable by Ultra-Violet radiation⁽¹⁾ (UV). UV erasure set all the EPROM memory cells to one and allows a reprogramming. The quartz window must be covered with an opaque label⁽²⁾ when the device is in operation. This is not so much to protect the EPROM array from inadvertent erasure, as to protect the RAM and other on-chip logic. Allowing light to impinge on the silicon die during device operation may cause a logical malfunction.

The TSC87251G2D products in plastic packages are One Time Programmable (OTP). Then an EPROM cell cannot be reset by UV once programmed to zero.

- Notes:
- 1. The recommended erasure procedure is exposure to ultra-violet light (at 2537 Å) to an integrated dose of at least 20 W-sec/cm². Exposing the EPROM to an ultra-violet lamp of 12000 μ W/cm² rating for 30 minutes should be sufficient.
- 2. Erasure of the EPROM begins to occur when the chip is exposed to light wavelength shorter than 4000 Å. Since sunlight and fluorescent light have wavelength in this range, exposure to these light sources over an extended time (1 week in sunlight or 3 years in room-level fluorescent lighting) could cause inadvertent erasure.

8.1.2 Mask ROM Devices

All the internal non-volatile memory of TSC83251G2D products is made of Mask ROM cells. They can only be verified by the user, using the same algorithm as the EPROM/OTPROM devices.

8.1.3 ROMless Devices

The TSC80251G2D products do not include on-chip Configuration Bytes, Code Memory and Encryption Array. They only include Signature Bytes made of Mask ROM cells which can be read using the same algorithm as the EPROM/OTPROM devices.

8.2 Security Features

In some microcontrollers applications, it is desirable that the user's program code be secured from unauthorized access. The TSC83251G2D and TSC87251G2D offer two kinds of protection for program code stored in the on-chip array:

- Program code in the on-chip Code Memory is encrypted when read out for verification if the Encryption Array is programmed.
- A three-level lock bit system restricts external access to the on-chip code memory.

8.2.1 Lock Bit System

The TSC87251G2D products implement 3 levels of security for User's program as described in Table 35. The TSC83251G2D products implement only the first level of security.

Level 0 is the level of an erased part and does not enable any security features.

Level 1 locks the programming of the User's internal Code Memory, the Configuration Bytes and the Encryption Array.

Level 2 locks the verifying of the User's internal Code Memory. It is always possible to verify the Configuration Bytes and the Lock Bits. It is never possible to verify the Encryption Array.

Level 3 locks the external execution.

Level	Lock bits LB[2:0]	Internal Execution	External Execution	Verification	Programming	External PROM read (MOVC)
0	000	Enable	Enable	Enable ⁽¹⁾	Enable	Enable ⁽²⁾
1	001	Enable	Enable	Enable ⁽¹⁾	Disable	Disable
2	01x ⁽³⁾	Enable	Enable	Disable	Disable	Disable
3	1xx ⁽³⁾	Enable	Disable	Disable	Disable	Disable

Table	35.	Lock	Bits	Programming
-------	-----	------	------	-------------

Notes:

1. Returns encrypted data if Encryption Array is programmed.

2. Returns non encrypted data.

3. x means don't care. Level 2 always enables level 1, and level 3 always enables levels 1 and 2.

The security level may be verified according to Table 36.

Table 36. Lock Bits Verifying

Level	Lock bits Data ⁽¹⁾
0	xxxxx000
1	xxxxx001
2	xxxxx01x
3	xxxxx1xx

Note:

1. x means don't care.

8.2.2 Encryption Array

The TSC83251G2D and TSC87251G2D products include a 128-byte Encryption Array located in non-volatile memory outside the memory address space. During verification of the on-chip code memory, the seven low-order address bits also address the Encryption Array. As the byte of the code memory is read, it is exclusive-NOR'ed (XNOR) with the key byte from the Encryption Array. If the Encryption Array is not programmed (still all 1s), the user program code is placed on the data bus in its original, unencrypted form. If the Encryption Array is programmed with key bytes, the user program code is encrypted and cannot be used without knowledge of the key byte sequence.

To preserve the secrecy of the encryption key byte sequence, the Encryption Array can not be verified. *Cautions:*

- 1. When a MOVC instruction is executed, the content of the ROM is not encrypted. In order to fully protect the user program code, the lock bit level 1 (see Table 35) must always be set when encryption is used.
- 2. If the encryption feature is implemented, the portion of the on-chip code memory that does not contain program code should be filled with "random" byte values to prevent the encryption key sequence from being revealed.



8.3 Signature Bytes

The TSC80251G2D derivatives contain factory-programmed Signature Bytes. These bytes are located in non-volatile memory outside the memory address space at 30h, 31h, 60h and 61h. To read the Signature Bytes, perform the procedure described in section 8.5, using the verify signature mode (see Table 39). Signature byte values are listed in Table 37.

		Signature Address	Signature Data
Vendor	ТЕМІС	30h	58h
Architecture	C251	31h	40h
Mamag	32 Kbytes EPROM or OTPROM	60h	F7h
Memory	32 Kbytes MaskROM or ROMless	OUI	77h
Revision	TSC80251G2D derivative	61h	FDh

Table 37. Signature Bytes (Electronic ID)

8.4 Programming Algorithm

Figure 9 shows the hardware setup needed to program the TSC87251G2D EPROM/OTPROM areas:

- The chip has to be put under reset and maintained in this state until the completion of the programming sequence.
- PSEN# and the other control signals (ALE and Port 0) have to be set to a high level.
- Then PSEN# has to be to forced to a low level after two clock cycles or more and it has to be maintained in this state until the completion of the programming sequence (see below).
- The voltage on the EA# pin must be set to V_{DD} .
- The programming mode is selected according to the code applied on Port 0 (see Table 38). It has to be applied until the completion of this programming operation.
- The programming address is applied on Ports 1 and 3 which are respectively the Most Significant Byte (MSB) and the Least Significant Byte (LSB) of the address.
- The programming data are applied on Port 2.
- The EPROM Programming is done by raising the voltage on the EA# pin to V_{PP} , then by generating a low level pulse on ALE/PROG# pin.
- $\bullet\,$ The voltage on the EA# pin must be lowered to V_{DD} before completing the programming operation.
- It is possible to alternate programming and verifying operation (See Paragraph 8.5). Please make sure the voltage on the EA# pin has actually been lowered to V_{DD} before performing the verifying operation.
- PSEN# and the other control signals have to be released to complete a sequence of programming operations or a sequence of programming and verifying operations.



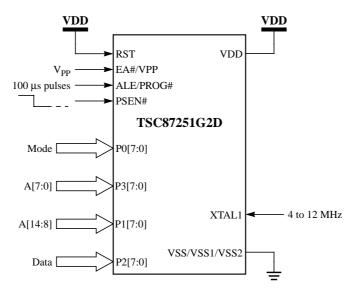


Figure 9. Setup for Programming

Table 38. Programming Modes

ROM Area ⁽¹⁾	RST	EA#/VPP	PSEN#	ALE/PROG# ⁽²⁾	PO	P2	P1(MSB) P3(LSB)
On-chip Code Memory	1	V _{PP}	0	1 Pulse	68h	Data	16-bit Address 0000h-7FFFh (32 Kbytes)
Configuration Bytes	1	V _{PP}	0	1 Pulse	69h	Data	CONFIG0: FFF8h CONFIG1: FFF9h
Lock Bits	1	V _{PP}	0	1 Pulse	6Bh	х	LB0: 0001h LB1: 0002h LB2: 0003h
Encryption Array	1	V _{PP}	0	1 Pulse	6Ch	Data	0000h-007Fh

Notes:

1. Signature Bytes are not user-programmable.

2. The ALE/PROG# pulse waveform is shown in Figure 31 page 54.

8.5 Verify Algorithm

Figure 10 shows the hardware setup needed to verify the TSC87251G2D EPROM/OTPROM or TSC83251G2D ROM areas:

- The chip has to be put under reset and maintained in this state until the completion of the verifying sequence.
- PSEN# and the other control signals (ALE and Port 0) have to be set to a high level.
- Then PSEN# has to be to forced to a low level after two clock cycles or more and it has to be maintained in this state until the completion of the verifying sequence (see below).
- The voltage on the EA# pin must be set to V_{DD} and ALE must be set to a high level.
- The Verifying Mode is selected according to the code applied on Port 0. It has to be applied until the completion of this verifying operation.
- The verifying address is applied on Ports 1 and 3 which are respectively the MSB and the LSB of the address.
- Then device is driving the data on Port 2.
- It is possible to alternate programming and verification operation (see Paragraph 8.4). Please make sure the voltage on the EA# pin has actually been lowered to V_{DD} before performing the verifying operation.
- PSEN# and the other control signals have to be released to complete a sequence of verifying operations or a sequence of programming and verifying operations.



ROM Area ⁽¹⁾	RST	EA#/VPP	PSEN#	ALE/PROG#	PO	P2	P1(MSB) P3(LSB)
On-chip code memory	1	1	0	1	28h	Data	16-bit Address 0000h-7FFFh (32 Kbytes)
Configuration Bytes	1	1	0	1	29h	Data	CONFIG0: FFF8h CONFIG1: FFF9h
Lock Bits	1	1	0	1	2Bh	Data	0000h
Signature Bytes	1	1	0	1	29h	Data	0030h, 0031h, 0060h, 0061h

Table 39. Verifying Modes

Note:

1. To preserve the secrecy of on-chip code memory when encrypted, the Encryption Array can not be verified.

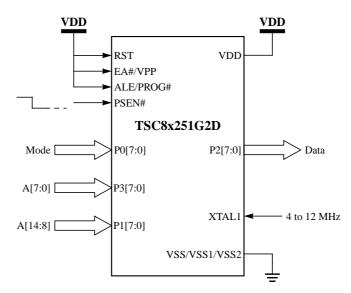


Figure 10. Setup for Verifying



9. Absolute Maximum Rating and Operating Conditions

9.1 Absolute Maximum Rating

Table 40. Absolute Maximum Ratings

•	Storage Temperature	-65 to +150°C
•	Voltage on any other Pin to VSS	-0.5 to +6.5 V
•	I _{OL} per I/O Pin	15 mA
•	Power Dissipation	1.5 W

9.2 Operating Conditions

Table 41. Operating Conditions

•	Ambient Temperature Under Bias	
	Commercial	0 to +70°C
	Industrial	-40 to +85°C
•	V _{DD} High Speed versions Low Voltage versions	

Note:

Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "operating conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.

10. DC Characteristics - Commercial & Industrial

10.1 DC Characteristics: High Speed versions - Commercial & Industrial

Table 42.	DC Character	istics: V _{DD} =	4.5 to 5.5	V. $T_{4} = -40$	to +85°C
14010 120	DO Character			$, A^{-} $	101 100 0

Symbol	Parameter	Min	Typical ⁽⁴⁾	Max	Units	Test Conditions
V _{IL}	Input Low Voltage (except EA#, SCL, SDA)	-0.5		0.2·V _{DD} - 0.1	v	
V _{IL1} ⁽⁵⁾	Input Low Voltage (SCL, SDA)	-0.5		0.3·V _{DD}	V	
V _{IL2}	Input Low Voltage (EA#)	0		0.2·V _{DD} - 0.3	v	
V _{IH}	Input high Voltage (except XTAL1, RST, SCL, SDA)	$0.2 \cdot V_{DD} + 0.9$		V _{DD} + 0.5	v	
V _{IH1} ⁽⁵⁾	Input high Voltage (XTAL1, RST, SCL, SDA)	$0.7 \cdot V_{DD}$		V _{DD} + 0.5	V	
V _{OL}	Output Low Voltage (Ports 1, 2, 3)			0.3 0.45 1.0	v	
V _{OL1}	Output Low Voltage (Ports 0, ALE, PSEN#, Port 2 in Page Mode during External Address)			0.3 0.45 1.0	v	$I_{OL} = 200 \ \mu A^{(1)(2)}$ $I_{OL} = 3.2 \ m A^{(1)(2)}$ $I_{OL} = 7.0 \ m A^{(1)(2)}$
V _{OH}	Output high Voltage (Ports 1, 2, 3, ALE, PSEN#)	$V_{DD} - 0.3$ $V_{DD} - 0.7$ $V_{DD} - 1.5$			v	$I_{OH} = -10 \ \mu A^{(3)}$ $I_{OH} = -30 \ \mu A^{(3)}$ $I_{OH} = -60 \ \mu A^{(3)}$
V _{OH1}	Output high Voltage (Port 0, Port 2 in Page Mode during External Address)	V _{DD} - 0.3 V _{DD} - 0.7 V _{DD} - 1.5			v	I _{OH} = -200 μA I _{OH} = -3.2 mA I _{OH} = -7.0 mA
V _{RET}	V _{DD} data retention limit			1.8	V	
I _{IL0}	Logical 0 Input Current (Ports 1, 2, 3)			- 50	μΑ	$V_{IN}=0.45$ V
I _{IL1}	Logical 1 Input Current (NMI)			+ 50	μΑ	V _{IN} = V _{DD}
I _{LI}	Input Leakage Current (Port 0)			± 10	μΑ	$0.45 \ V < V_{IN} < V_{DD}$
I _{TL}	Logical 1-to-0 Transition Current (Ports 1, 2, 3 - AWAIT#)			- 650	μΑ	V _{IN} = 2.0 V
R _{RST}	RST Pull-Down Resistor	40	110	225	kΩ	
C _{IO}	Pin Capacitance		10		pF	$T_A = 25^{\circ}C$
I _{DD}	Operating Current		20 25 35	25 30 40	mA	$\begin{array}{l} F_{OSC} = 12 \ \text{MHz} \\ F_{OSC} = 16 \ \text{MHz} \\ F_{OSC} = 24 \ \text{MHz} \end{array}$
I _{DL}	Idle Mode Current		5 6.5 9.5	6 8 12	mA	$\begin{array}{l} F_{OSC} = 12 \ \text{MHz} \\ F_{OSC} = 16 \ \text{MHz} \\ F_{OSC} = 24 \ \text{MHz} \end{array}$
I _{PD}	Power-Down Current		2	20	μΑ	$V_{RET} < V_{DD} < 5.5 \ V$
V _{PP}	Programming supply voltage	12.5		13	v	$T_A = 0$ to $+40^{\circ}C$
I _{PP}	Programming supply current			75	mA	$T_A = 0$ to $+40^{\circ}C$

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TSC80251G2D

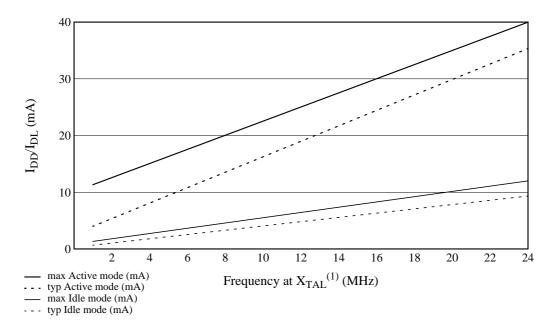
Notes:

1. Under steady-state (non-transient) conditions, I_{OL} must be externally limited as follows:

Maximum I _{OL} per port pin:	
Maximum I _{OL} per 8-bit port:	Port 0
	Ports 1-315 mA
Maximum Total I _{OL} for all:	Output Pins 71 mA
If Los exceeds the test conditions V.	may exceed the related spec

If I_{OL} exceeds the test conditions, V_{OL} may exceed the related specification. Pins are not guaranteed to sink current greater than the listed test conditions.

- 2. Capacitive loading on Ports 0 and 2 may cause spurious noise pulses above 0.4 V on the low-level outputs of ALE and Ports 1, 2, and 3. The noise is due to external bus capacitance discharging into the Port 0 and Port 2 pins when these pins change from high to low. In applications where capacitive loading exceeds 100 pF, the noise pulses on these signals may exceed 0.8 V. It may be desirable to qualify ALE or other signals with a Schmitt Trigger or CMOS-level input logic.
- 3. Capacitive loading on Ports 0 and 2 causes the V_{OH} on ALE and PSEN# to drop below the specification when the address lines are stabilizing.
- 4. Typical values are obtained using $V_{DD} = 5$ V and $T_A = 25^{\circ}C$. They are not tested and there is not guarantee on these values.
- The input threshold voltage of SCL and SDA meets the l²C specification, so an input voltage below 0.3·V_{DD} will be recognized as a logic 0 while an input voltage above 0.7·V_{DD} will be recognized as a logic 1.



Note:

1. The clock prescaler is not used: $F_{OSC} = F_{XTAL}$.



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10.2 DC Characteristics: Low Voltage versions - Commercial & Industrial

Table 43. DC Characteristics; $V_{DD}{=}$ 2.7 to 5.5 V, $T_{A}{=}$ -40 to +85°C

Symbol	Parameter	Min	Typical ⁽⁴⁾	Max	Units	Test Conditions
V_{IL}	Input Low Voltage (except EA#, SCL, SDA)	-0.5		0.2·V _{DD} - 0.1	V	
V _{IL1} ⁽⁵⁾	Input Low Voltage (SCL, SDA)	-0.5		0.3·V _{DD}	v	
V _{IL2}	Input Low Voltage (EA#)	0		0.2·V _{DD} - 0.3	V	
V _{IH}	Input high Voltage (except XTAL1, RST, SCL, SDA)	$0.2 \cdot V_{DD} + 0.9$		V _{DD} + 0.5	V	
$V_{IH1}^{(5)}$	Input high Voltage (XTAL1, RST, SCL, SDA)	$0.7 \cdot V_{DD}$		V _{DD} + 0.5	v	
V _{OL}	Output Low Voltage (Ports 1, 2, 3)			0.45	v	$I_{OL} = 0.8 \text{ mA}^{(1)(2)}$
V _{OL1}	Output Low Voltage (Ports 0, ALE, PSEN#, Port 2 in Page Mode during External Address)			0.45	V	I_{OL} = 1.6 mA ⁽¹⁾⁽²⁾
V _{OH}	Output high Voltage (Ports 1, 2, 3, ALE, PSEN#)	$0.9 \cdot V_{DD}$			v	I_{OH} = -10 $\mu A^{(3)}$
V _{OH1}	Output high Voltage (Port 0, Port 2 in Page Mode during External Address)	0.9·V _{DD}			v	I _{OH} = -40 μA
V _{RET}	V _{DD} data retention limit			1.8	V	
I _{IL0}	Logical 0 Input Current (Ports 1, 2, 3 - AWAIT#)			- 50	μΑ	$V_{IN}=0.45$ V
I _{IL1}	Logical 1 Input Current (NMI)			+ 50	μΑ	V _{IN} = V _{DD}
I _{LI}	Input Leakage Current (Port 0)			± 10	μΑ	$0.45 \ V < V_{IN} < V_{DD}$
I _{TL}	Logical 1-to-0 Transition Current (Ports 1, 2, 3)			- 650	μΑ	V _{IN} = 2.0 V
R _{RST}	RST Pull-Down Resistor	40	110	225	kΩ	
C _{IO}	Pin Capacitance		10		pF	$T_A = 25^{\circ}C$
I _{DD}	Operating Current		4 8 9 11	8 11 12 14	mA	$\begin{array}{c} 5 \ \mbox{MHz}, \ \mbox{V}_{DD} < 3.6 \ \mbox{V} \\ 10 \ \ \mbox{MHz}, \ \ \mbox{V}_{DD} < 3.6 \ \ \mbox{V} \\ 12 \ \ \ \mbox{MHz}, \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$
I _{DL}	Idle Mode Current		0.5 1.5 2 3	1 4 5 7	mA	$\begin{array}{c} 5 \ \mathrm{MHz}, \ \mathrm{V_{DD}} < 3.6 \ \mathrm{V} \\ 10 \ \mathrm{MHz}, \ \mathrm{V_{DD}} < 3.6 \ \mathrm{V} \\ 12 \ \mathrm{MHz}, \ \mathrm{V_{DD}} < 3.6 \ \mathrm{V} \\ 16 \ \mathrm{MHz}, \ \mathrm{V_{DD}} < 3.6 \ \mathrm{V} \end{array}$
I _{PD}	Power-Down Current		1	10	μΑ	$V_{RET} < V_{DD} < 3.6 V$

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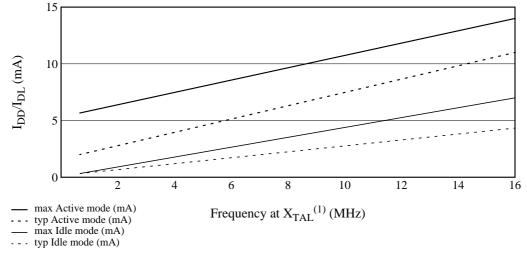
Notes:

1. Under steady-state (non-transient) conditions, I_{OL} must be externally limited as follows:

Maximum I _{OL} per port pin:		10 mA
Maximum I _{OL} per 8-bit port:	Port 0	26 mA
	Ports 1-3	15 mA
Maximum Total I _{OL} for all:	Output Pins	71 mA
If I_{OI} exceeds the test conditions. V_{OI}	may exceed the 1	elated specifi

If I_{OL} exceeds the test conditions, V_{OL} may exceed the related specification. Pins are not guaranteed to sink current greater than the listed test conditions.

- 2. Capacitive loading on Ports 0 and 2 may cause spurious noise pulses above 0.4 V on the low-level outputs of ALE and Ports 1, 2, and 3. The noise is due to external bus capacitance discharging into the Port 0 and Port 2 pins when these pins change from high to low. In applications where capacitive loading exceeds 100 pF, the noise pulses on these signals may exceed 0.8 V. It may be desirable to qualify ALE or other signals with a Schmitt Trigger or CMOS-level input logic.
- 3. Capacitive loading on Ports 0 and 2 causes the V_{OH} on ALE and PSEN# to drop below the specification when the address lines are stabilizing.
- 4. Typical values are obtained using $V_{DD}=3$ V and $T_A=25^{\circ}C$. They are not tested and there is not guarantee on these values.
- The input threshold voltage of SCL and SDA meets the l²C specification, so an input voltage below 0.3·V_{DD} will be recognized as a logic 0 while an input voltage above 0.7·V_{DD} will be recognized as a logic 1.



Note:

1. The clock prescaler is not used: $F_{OSC} = F_{XTAL}$.

Figure 12. I_{DD}/I_{DL} Versus X_{TAL} Frequency; V_{DD} = 2.7 to 3.6 V



10.3 DC Characteristics: I_{DD} , I_{DL} and I_{PD} Test Conditions

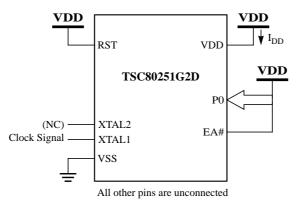


Figure 13. I_{DD} Test Condition, Active Mode

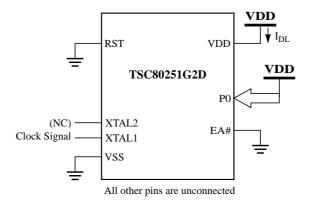


Figure 14. I_{DL} Test Condition, Idle Mode

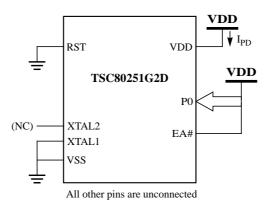


Figure 15. I_{PD} Test Condition, Power-Down Mode



11. AC Characteristics - Commercial & Industrial

11.1 AC Characteristics - External Bus Cycles

Definition of symbols

Table 44. External Bus Cycles Timing Symbol Definitions

Signals				
А	Address			
D	Data In			
L	ALE			
Q	Data Out			
R	RD#/PSEN#			
W	WR#			

Conditions				
Н	High			
L	Low			
v	Valid			
Х	No Longer Valid			
Z	Floating			

Timings

Test conditions: capacitive load on all pins= 50 pF.

Table 45 and Table 46 list the AC timing parameters for the TSC80251G2D derivatives with no wait states. External wait states can be added by extending PSEN#/RD#/WR# and or by extending ALE. In these tables, Note 2 marks parameters affected by one ALE wait state, and Note 3 marks parameters affected by PSEN#/RD#/WR# wait states.

Figure 16 to Figure 21 show the bus cycles with the timing parameters.

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Generalised	Deres der	12 MHz		16 MHz		24 MHz		
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Unit
T _{OSC}	1/F _{OSC}	83		62		41		ns
T _{LHLL}	ALE Pulse Width	78		58		38		ns ⁽²⁾
T _{AVLL}	Address Valid to ALE Low	78		58		37		ns ⁽²⁾
T _{LLAX}	Address hold after ALE Low	19		11		3		ns
T _{RLRH} ⁽¹⁾	RD#/PSEN# Pulse Width	162		121		78		ns ⁽³⁾
T _{WLWH}	WR# Pulse Width	165		124		81		ns ⁽³⁾
T _{LLRL} ⁽¹⁾	ALE Low to RD#/PSEN# Low	22		14		6		ns
T _{LHAX}	ALE High to Address Hold	99		70		40		ns ⁽²⁾
T _{RLDV} ⁽¹⁾	RD#/PSEN# Low to Valid Data		146		104		61	ns ⁽³⁾
T _{RHDX} ⁽¹⁾	Data Hold After RD#/PSEN# High	0		0		0		ns
T _{RHAX} ⁽¹⁾	Address Hold After RD#/PSEN# High	0		0		0		ns
T _{RLAZ} ⁽¹⁾	RD#/PSEN# Low to Address Float		0		0		0	ns
T _{RHDZ1}	Instruction Float After RD#/PSEN# High		45		40		30	ns
T _{RHDZ2}	Data Float After RD#/PSEN# High		215		165		115	ns
T _{RHLH1}	RD#/PSEN# high to ALE High (Instruction)	49		43		31		ns
T _{RHLH2}	RD#/PSEN# high to ALE High (Data)	215		169		115		ns
T _{WHLH}	WR# High to ALE High	215		169		115		ns
T _{AVDV1}	Address (P0) Valid to Valid Data In		250		175		105	ns ⁽²⁾⁽³⁾
T _{AVDV2}	Address (P2) Valid to Valid Data In		306		223		140	ns ⁽²⁾⁽³⁾
T _{AVDV3}	Address (P0) Valid to Valid Instruction In		150		109		68	ns ⁽³⁾
T _{AXDX}	Data Hold after Address Hold	0		0		0		ns
T _{AVRL} ⁽¹⁾	Address Valid to RD# Low	100		70		40		ns ⁽²⁾
T _{AVWL1}	Address (P0) Valid to WR# Low	100		70		40		ns ⁽²⁾
T _{AVWL2}	Address (P2) Valid to WR# Low	158		115		74		ns ⁽²⁾
T _{WHQX}	Data Hold after WR# High	90		69		32		ns
T _{QVWH}	Data Valid to WR# High	133		102		72		ns ⁽³⁾
T _{WHAX}	WR# High to Address Hold	167		125		84		ns

Table 45. Bus Cycles AC Timings; $V_{DD}{=}$ 4.5 to 5.5 V, $T_{A}{=}$ -40 to $85^{\circ}C$

Notes:

1. Specification for PSEN# are identical to those for RD#.

If a wait state is added by extending ALE, add 2·T_{OSC}.
 If wait states are added by extending RD#/PSEN#/WR#, add 2N·T_{OSC} (N= 1..3).



Ghh	Desemator		MHz	16 MHz		T T 1
Symbol	Parameter	Min	Max	Min	Max	Unit
T _{OSC}	1/F _{OSC}	83		62		ns
T _{LHLL}	ALE Pulse Width	72		52		ns ⁽²⁾
T _{AVLL}	Address Valid to ALE Low	71		51		ns ⁽²⁾
T _{LLAX}	Address hold after ALE Low	14		6		ns
T _{RLRH} ⁽¹⁾	RD#/PSEN# Pulse Width	163		121		ns ⁽³⁾
T _{WLWH}	WR# Pulse Width	165		124		ns ⁽³⁾
T _{LLRL} ⁽¹⁾	ALE Low to RD#/PSEN# Low	17		11		ns
T _{LHAX}	ALE High to Address Hold	90		57		ns ⁽²⁾
T _{RLDV} ⁽¹⁾	RD#/PSEN# Low to Valid Data		133		92	ns ⁽³⁾
T _{RHDX} ⁽¹⁾	Data Hold After RD#/PSEN# High	0		0		ns
T _{RHAX} ⁽¹⁾	Address Hold After RD#/PSEN# High	0		0		ns
T _{RLAZ} ⁽¹⁾	RD#/PSEN# Low to Address Float		0		0	ns
T _{RHDZ1}	Instruction Float After RD#/PSEN# High		59		48	ns
T _{RHDZ2}	Data Float After RD#/PSEN# High		225		175	ns
T _{RHLH1}	RD#/PSEN# high to ALE High (Instruction)	60		47		ns
T _{RHLH2}	RD#/PSEN# high to ALE High (Data)	226		172		ns
T _{WHLH}	WR# High to ALE High	226		172		ns
T _{AVDV1}	Address (P0) Valid to Valid Data In		289		160	ns ⁽²⁾⁽³⁾
T _{AVDV2}	Address (P2) Valid to Valid Data In		296		211	ns ⁽²⁾⁽³⁾
T _{AVDV3}	Address (P0) Valid to Valid Instruction In		144		98	ns ⁽³⁾
T _{AXDX}	Data Hold after Address Hold	0		0		ns
T _{AVRL} ⁽¹⁾	Address Valid to RD# Low	111		64		ns ⁽²⁾
T _{AVWL1}	Address (P0) Valid to WR# Low	111		64		ns ⁽²⁾
T _{AVWL2}	Address (P2) Valid to WR# Low	158		116		ns ⁽²⁾
T _{WHQX}	Data Hold after WR# High	82		66		ns
T _{QVWH}	Data Valid to WR# High	135		103		ns ⁽³⁾
T _{WHAX}	WR# High to Address Hold	168		125		ns
			-			

Table 46. Bus Cycles AC Timings; $V_{DD}{=}$ 2.7 to 5.5 V, $T_{A}{=}$ -40 to 85°C

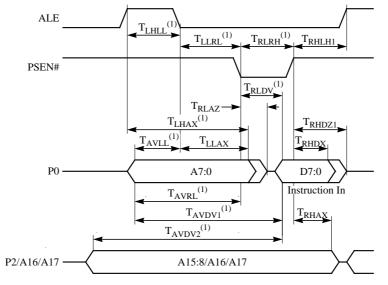
Notes:

1. Specification for PSEN# are identical to those for RD#.

If a wait state is added by extending ALE, add 2.T_{OSC}.
 If wait states are added by extending RD#/PSEN#/WR#, add 2N·T_{OSC} (N= 1..3).

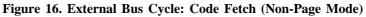


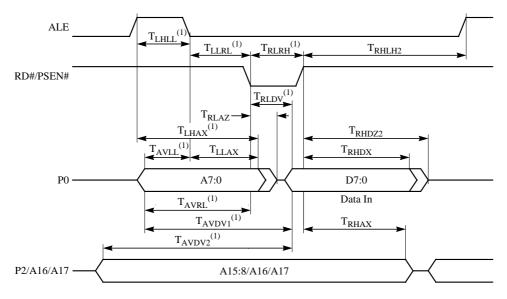
Waveforms in Non-Page Mode



Note:

1. The value of this parameter depends on wait states. See Table 45 and Table 46.





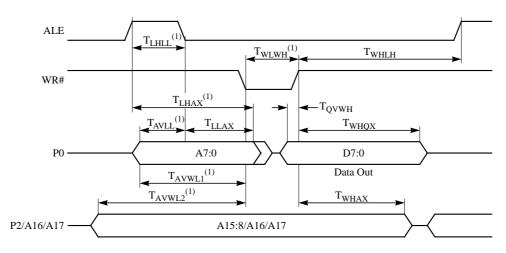
Note:

1. The value of this parameter depends on wait states. See Table 45 and Table 46.

Figure 17. External Bus Cycle: Data Read (Non-Page Mode)

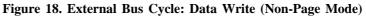
TEMIC Semiconductors

TSC80251G2D

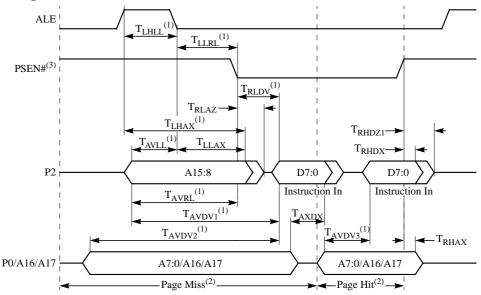


Note:

1. The value of this parameter depends on wait states. See Table 45 and Table 46.



Waveforms in Page Mode

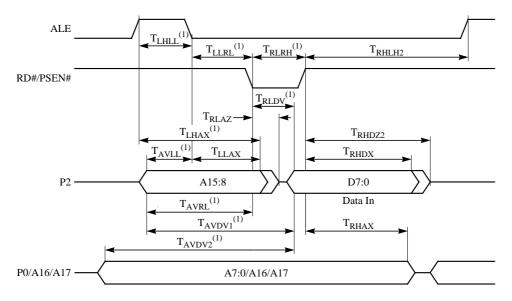


Notes:

- 1. The value of this parameter depends on wait states. See Table 45 and Table 46.
- 2. A page hit (i.e., a code fetch to the same 256-byte "page" as the previous code fetch) requires one state $(2 \cdot T_{OSC})$; a page miss requires two states $(4 \cdot T_{OSC})$.
- 3. During a sequence of page hits, PSEN# remains low until the end of the last page-hit cycle.

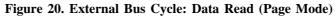
Figure 19. External Bus Cycle: Code Fetch (Page Mode)

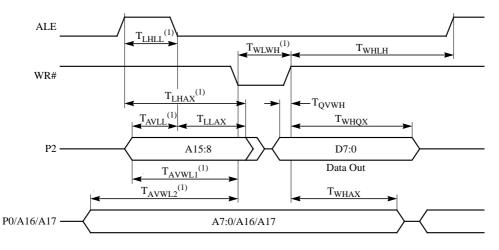




Note:

1. The value of this parameter depends on wait states. See Table 45 and Table 46.





Note:

1. The value of this parameter depends on wait states. See Table 45 and Table 46.

Figure 21. External Bus Cycle: Data Write (Page Mode)



11.2 AC Characteristics - Real-Time Synchronous Wait State

Definition of symbols

Signals				
С	WCLK			
R	RD#/PSEN#			
W	WR#			
Y	WAIT#			

Conditions				
L Low				
V	Valid			
Х	No Longer Valid			

Timings

Table 48. Real-Time Synchronous Wait AC Timings; V_{DD} = 2.7 to 5.5 V, T_A = -40 to 85°C

Table 47. Real-Time Synchronous Wait Timing Symbol Definitions

Symbol	Parameter	Min	Max	Unit
T _{CLYV}	Wait Clock Low to Wait Set-up	0	T _{OSC} - 20	ns
T _{CLYX}	Wait Hold after Wait Clock Low	$2W \cdot T_{OSC} + 5$	(1+2W)·T _{OSC} - 20	ns
T _{RLYV}	PSEN#/RD# Low to Wait Set-up	0	T _{OSC} - 20	ns
T _{RLYX}	Wait Hold after PSEN#/RD# Low	$2W \cdot T_{OSC} + 5$	(1+2W)·T _{OSC} - 20	ns
T _{WLYV}	WR# Low to Wait Set-up	0	T _{OSC} - 20	ns
T _{WLYX}	Wait Hold after WR# Low	$2W \cdot T_{OSC} + 5$	(1+2W)·T _{OSC} - 20	ns

Waveforms

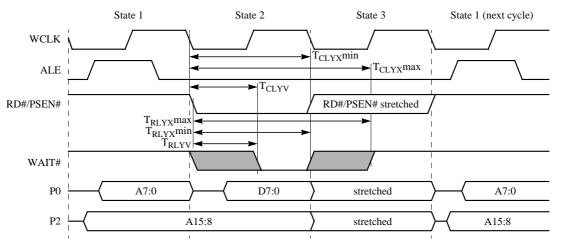


Figure 22. Real-time Synchronous Wait State: Code Fetch/Data Read



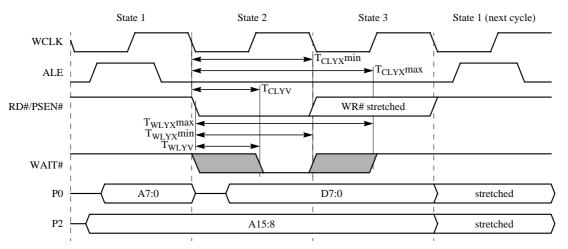


Figure 23. Real-time Synchronous Wait State: Data Write

11.3 AC Characteristics - Real-Time Asynchronous Wait State

Definition of symbols

Table 49. Real-Time Asynchronous Wait Timing Symbol Definitions

Signals		
S	PSEN#/RD#/WR#	
Y	AWAIT#	

Conditions				
L Low				
V	Valid			
X No Longer Valid				

Timings

Symbol	Parameter	Min	Max	Unit
T _{SLYV}	PSEN#/RD#/WR# Low to Wait Set-up		T _{OSC} - 10	ns
T _{SLYX}	Wait Hold after PSEN#/RD#/WR# Low	$(2N-1) \cdot T_{OSC} + 10$		ns ⁽¹⁾

Note:

1. N is the number of wait states added ($N \ge 1$).

Waveforms

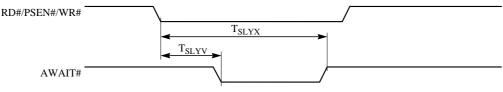


Figure 24. Real-time Asynchronous Wait State Timings



11.4 AC Characteristics - Serial Port in Shift Register Mode

Definition of symbols

Signals		
D	Data In	
Q	Data Out	
X	Clock	

Conditions		
Н	High	
L	Low	
v	Valid	
Х	No Longer Valid	

Timings

Table 52. Serial Port AC Timing -Shift Register Mode; V_{DD} = 2.7 to 5.5 V, T_A = -40 to 85°C

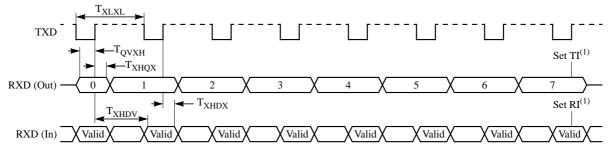
Table 51. Serial Port Timing Symbol Definitions

Symbol Parameter		12 MHz		16 MHz		24 MHz ⁽¹⁾		Unit	
Symbol	Symbol Farameter		Max	Min	Max	Min	Max	Omt	
T _{XLXL}	Serial Port Clock Cycle Time	998		749		500		ns	
T _{QVXH}	Output Data Setup to Clock Rising Edge	833		625		417		ns	
T _{XHQX}	Output Data hold after Clock Rising Edge	165		124		82		ns	
T _{XHDX}	Input Data Hold after Clock Rising Edge	0		0		0		ns	
T _{XHDV}	Clock Rising Edge to Input Data Valid		974		732		482	ns	

Note:

1. For high speed versions only.

Waveforms



Note:

1. TI and RI are set during SIP1 of the peripheral cycle following the shift of the eight bit.

Figure 25. Serial Port Waveforms - Shift Register Mode

11.5 AC Characteristics - SSLC: I²C Interface

Timings

Symbol	Parameter	INPUT	INPUT		OUTPUT	
Symbol	rarameter	Min	Max	Min	Max	
Thd; STA	Start condition hold time	14·TCLCL ⁽⁴⁾		4.0 μs ⁽¹⁾		
TLOW	SCL low time	16·TCLCL ⁽⁴⁾		4.7 μs ⁽¹⁾		
Thigh	SCL high time	14·TCLCL ⁽⁴⁾		4.0 μs ⁽¹⁾		
TRC	SCL rise time		1 µs		_(2)	
TFC	SCL fall time		0.3 µs		$0.3 \ \mu s^{(3)}$	
Tsu; DAT1	Data set-up time	250 ns		20.TCLCL ⁽⁴⁾ - TRD	l .	
Tsu; DAT2	SDA set-up time (before repeated START condition)	250 ns		1 µs ⁽¹⁾		
Tsu; DAT3	SDA set-up time (before STOP condition)	250 ns		8-TCLCL ⁽⁴⁾		
Thd; DAT	Data hold time	0 ns		8-TCLCL ⁽⁴⁾ - TFC		
TSU; STA	Repeated START set-up time	14·TCLCL ⁽⁴⁾		4.7 μs ⁽¹⁾		
Tsu; STO	STOP condition set-up time	14-TCLCL ⁽⁴⁾		4.0 μs ⁽¹⁾		
TBUF	Bus free time	14·TCLCL ⁽⁴⁾		4.7 μs ⁽¹⁾		
Trd	SDA rise time		1 µs		_(2)	
Tfd	SDA fall time		0.3 µs		$0.3~\mu s^{(3)}$	

Notes:

1. At 100 kbit/s. At other bit-rates this value is inversely proportional to the bit-rate of 100 kbit/s.

2. Determined by the external bus-line capacitance and the external bus-line pull-up resistor, this must be $< 1 \ \mu s$.

3. Spikes on the SDA and SCL lines with a duration of less than 3. TCLCL will be filtered out. Maximum capacitance on bus-lines SDA and SCL= 400 pF.

4. $TCLCL = T_{OSC} = one oscillator clock period.$

Waveforms

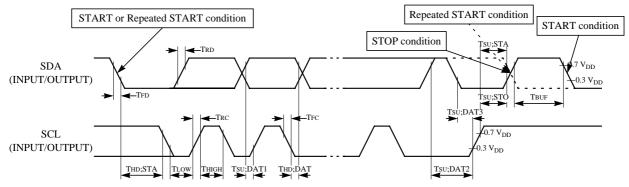


Figure 26. I²C Waveforms



11.6 AC Characteristics - SSLC: SPI Interface

Definition of symbols

Signals	
С	Clock
Ι	Data In
0	Data Out
S	SS#

Table 54. SPI Interface Timing Symbol Definitions

Conditions		
Н	High	
L	Low	
V	Valid	
X	No Longer Valid	
Z	Floating	

Timings

Table 55. SPI Interface AC Timing; $V_{DD}\text{=}$ 2.7 to 5.5 V, $T_{A}\text{=}$ -40 to 85°C

Symbol	Parameter	Min	Max	Unit
Slave mode ⁽¹⁾	-			-
T _{CHCH}	Clock Period	8		T _{OSC}
T _{CHCX}	Clock High Time	3.2		T _{OSC}
T _{CLCX}	Clock Low Time	3.2		T _{OSC}
T _{SLCH} , T _{SLCL}	SS# Low to Clock edge	200		ns
T _{IVCL} , T _{IVCH}	Input Data Valid to Clock Edge	100		ns
T _{CLIX} , T _{CHIX}	Input Data Hold after Clock Edge	100		ns
T _{CLOV} , T _{CHOV}	Output Data Valid after Clock Edge		100	ns
T _{CLOX} , T _{CHOX}	Output Data Hold Time after Clock Edge	0		ns
T _{CLSH} , T _{CHSH}	SS# High after Clock Edge	0		ns
T _{IVCL} , T _{IVCH}	Input Data Valid to Clock Edge	100		ns
T _{CLIX} , T _{CHIX}	Input Data Hold after Clock Edge	100		ns
T _{SLOV}	SS# Low to Output Data Valid		130	ns
T _{SHOX}	Output Data Hold after SS# High		130	ns
T _{SHSL}	SS# High to SS# Low	(2)		
T _{ILIH}	Input Rise Time		2	μs
T _{IHIL}	Input Fall Time		2	μs
T _{OLOH}	Output Rise time		100	ns
T _{OHOL}	Output Fall Time		100	ns

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Symbol	Parameter	Min	Max	Unit
Master mode ⁽³⁾	,	I		
T _{CHCH}	Clock Period	4		T _{OSC}
T _{CHCX}	Clock High Time	1.6		T _{OSC}
T _{CLCX}	Clock Low Time	1.6		T _{OSC}
T _{IVCL} , T _{IVCH}	Input Data Valid to Clock Edge	50		ns
T _{CLIX} , T _{CHIX}	Input Data Hold after Clock Edge	50		ns
T _{CLOV,} T _{CHOV}	Output Data Valid after Clock Edge		65	ns
T _{CLOX} , T _{CHOX}	Output Data Hold Time after Clock Edge	0		ns
T _{ILIH}	Input Data Rise Time		2	μs
T _{IHIL}	Input Data Fall Time		2	μs
T _{OLOH}	Output Data Rise time		50	ns
T _{OHOL}	Output Data Fall Time		50	ns

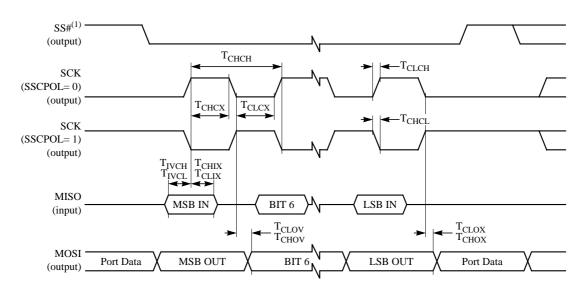
Notes:

1. Capacitive load on all pins= 200 pF in slave mode.

2. The value of this parameter depends on software.

3. Capacitive load on all pins= 100 pF in master mode.

Waveforms



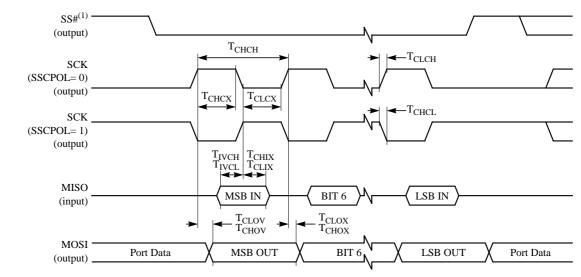
Note:

1. SS# handled by software.



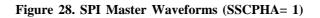
TEMIC Semiconductors

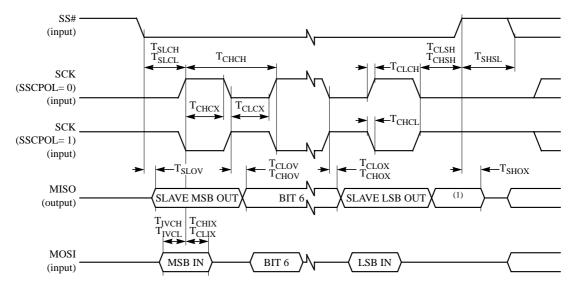
TSC80251G2D



Note:

1. SS# handled by software.



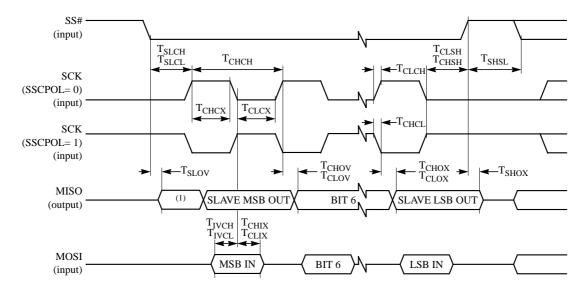


Note:

1. Not Defined but normally MSB of character just received.

Figure 29. SPI Slave Waveforms (SSCPHA= 0)





Note:

1. Not Defined but generally the LSB of the character which has just been received.

Figure 30. SPI Slave Waveforms (SSCPHA= 1)



11.7 AC Characteristics - EPROM Programming and Verifying

Definition of symbols

Signals		
А	Address	
Е	Enable: mode set on Port 0	
G	Program	
Q	Data Out	
S	Supply (V _{PP})	

Conditions		
Н	High	
L	Low	
V	Valid	
X	No Longer Valid	
Z	Floating	

Address H High

Table 56. EPROM Programming and Verifying Timing Symbol Definitions

Timings

Symbol	Parameter	Min	Max	Unit
T _{OSC}	XTAL1 Period	83.5	250	ns
T _{AVGL}	Address Setup to PROG# low	48		T _{OSC}
T _{GHAX}	Address Hold after PROG# low	48		T _{OSC}
T _{DVGL}	Data Setup to PROG# low	48		T _{OSC}
T _{GHDX}	Data Hold after PROG#	48		T _{OSC}
T _{ELSH}	ENABLE High to V _{PP}	48		T _{OSC}
T _{SHGL}	V _{PP} Setup to PROG# low	10		μs
T _{GHSL}	V _{PP} Hold after PROG#	10		μs
T _{SLEH}	ENABLE Hold after V _{PP}	0		ns
T _{GLGH}	PROG# Width	90	110	μs

Table 58. EPROM Verifying AC timings; $V_{DD}{=}$ 4.5 to 5.5 V, $V_{DD}{=}$ 2.7 to 5.5 V, $T_{A}{=}$ 0 to 40°C

Symbol	Parameter	Min	Max	Unit
T _{OSC}	XTAL1 Period	83.5	250	ns
T _{AVQV}	Address to Data Valid		48	T _{OSC}
T _{AXQX}	Address to Data Invalid	0		ns
T _{ELQV}	ENABLE low to Data Valid	0	48	T _{OSC}
T _{EHQZ}	Data Float after ENABLE	0	48	T _{OSC}

TEMIC

Waveforms

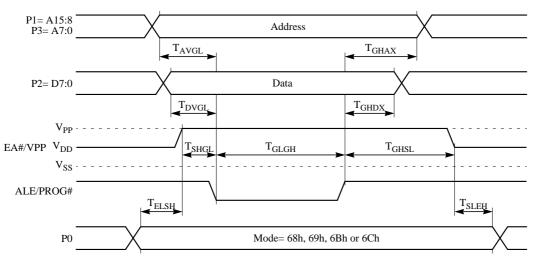


Figure 31. EPROM Programming Waveforms

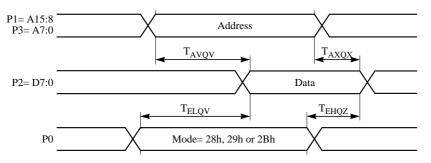


Figure 32. EPROM Verifying Waveforms



11.8 AC Characteristics - External Clock Drive and Logic Level References

Definition of symbols

Table 59. External Clock Timing Symbol Definitions

Signals				
С	Clock			

Conditions				
Н	High			
L	Low			
Х	No Longer Valid			

Timings

Table 60. External Clock AC Timings; V_{DD} = 4.5 to 5.5 V, T_A = -40 to +85°C

Symbol	Parameter	Min	Max	Unit
F _{OSC}	Oscillator Frequency		24	MHz
T _{CHCX}	High Time	10		ns
T _{CLCX}	Low Time	10		ns
T _{CLCH}	Rise Time	3		ns
T _{CHCL}	Fall Time	3		ns

Waveforms

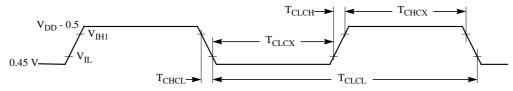
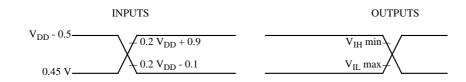


Figure 33. External Clock Waveform



Note:

During AC testing, all inputs are driven at V_{DD} -0.5 V for a logic 1 and 0.45 V for a logic 0. Timing measurements are made on all outputs at V_{IH} min for a logic 1 and V_{IL} max for a logic 0.

Figure 34. AC Testing Input/Output Waveforms



Note:

For timing purposes, a port pin is no longer floating when a 100 mV change from load voltage occurs and begins to float when a 100 mV change from the loading V_{OH}/V_{OL} level occurs with I_{OL}/I_{OH} = ±20 mA.

Figure 35. Float Waveforms

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12. Packages

12.1 List of Packages

- PDIL 40
- CDIL 40 with window
- PLCC 44
- CQPJ 44 with window
- VQFP 44 (10x10)

12.2 PDIL 40 - Mechanical Outline

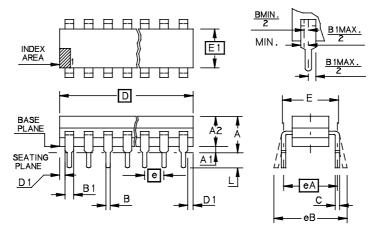


Figure 36. Plastic Dual In Line

Table 61. PDIL Package Size

	MM		IN	СН
	Min	Max	Min	Max
А	-	5.08	-	.200
A1	0.38	-	.015	-
A2	3.18	4.95	.125	.195
В	0.36	0.56	.014	.022
B1	0.76	1.78	.030	.070
С	0.20	0.38	.008	.015
D	50.29	53.21	1.980	2.095
Е	15.24	15.87	.600	.625
E1	12.32	14.73	.485	.580
e	2.54	B.S.C.	.100 I	B.S.C.
eA	15.24	B.S.C.	.600 B.S.C.	
eB	-	17.78	-	.700
L	2.93	3.81	.115	.150
D1	0.13	-	.005	-

12.3 CDIL 40 with Window - Mechanical Outline

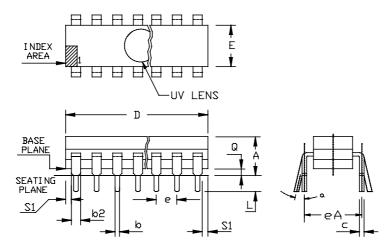


Figure 37. Ceramic Dual In Line

Table 6	2. CDIL	Package	Size
---------	---------	---------	------

	MM		IN	СН
	Min	Max	Min	Max
А	-	5.71	-	.225
b	0.36	0.58	.014	.023
b2	1.14	1.65	.045	.065
с	0.20	0.38	.008	.015
D	-	53.47	-	2.105
Е	13.06	15.37	.514	.605
e	2.54 1	B.S.C.	.100	B.S.C.
eA	15.24	B.S.C.	.600	B.S.C.
L	3.18	5.08	.125	.200
Q	0.38	1.40	.015	.055
S 1	0.13	-	.005	-
a	0 - 15		0 -	- 15
Ν	40			



12.4 PLCC 44 - Mechanical Outline

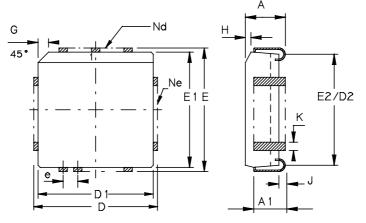


Figure 38. Plastic Lead Chip Carrier

 Table 63. PLCC Package Size

	MM		IN	СН
	Min	Max	Min	Max
А	4.20	4.57	.165	.180
A1	2.29	3.04	.090	.120
D	17.40	17.65	.685	.695
D1	16.44	16.66	.647	.656
D2	14.99	16.00	.590	.630
Е	17.40	17.65	.685	.695
E1	16.44	16.66	.647	.656
E2	14.99	16.00	.590	.630
e	1.27	BSC	.050 BSC	
G	1.07	1.22	.042	.048
Н	1.07	1.42	.042	.056
J	0.51	-	.020	-
K	0.33	0.53	.013	.021
Nd	11 11		1	
Ne	1	1	1	1

12.5 CQPJ 44 with Window - Mechanical Outline

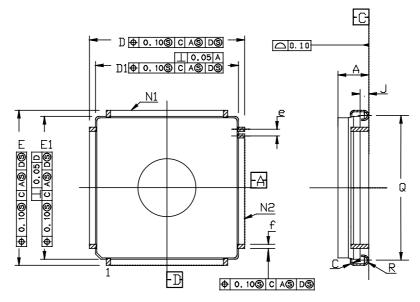


Figure 39. Ceramic Quad Pack J

Table 64. CQPJ Package size

	ММ		IN	СН
	Min	Max	Min	Max
А	-	4.90	-	.193
С	0.15	0.25	.006	.010
D - E	17.40	17.55	.685	.691
D1 - E1	16.36	16.66	.644	.656
e	1.27	ТҮР	.050 TYP	
f	0.43	0.53	.017	.021
J	0.86	1.12	.034	.044
Q	15.49	16.00	.610	.630
R	0.86	0.86 TYP		ТҮР
N1	11		1	1
N2	1	11		1



12.6 VQFP 44 (10x10) - Mechanical Outline

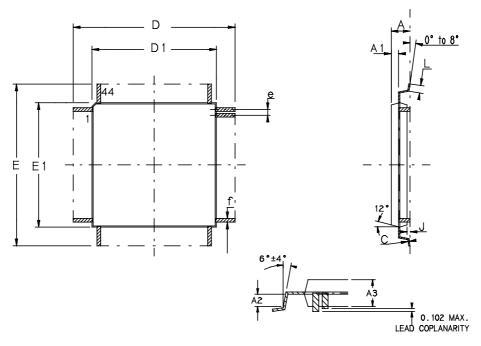


Figure 40. Shrink Quad Flat Pack (Plastic)

Table	65.	VQFP	Package	Size
-------	-----	------	---------	------

	ММ		IN	СН
	Min	Max	Min	Max
A	-	1.60	-	.063
A1	0.64	REF	.025	REF
A2	0.64	REF	.025	REF
A3	1.35	1.45	.053	.057
D	11.90	12.10	.468	.476
D1	9.90	10.10	.390	.398
Е	11.90	12.10	.468	.476
E1	9.90	10.10	.390	.398
J	0.05	-	.002	6
L	0.45	0.75	.018	.030
e	0.80 BSC		.0315	BSC
f	0.35 BSC		.014	BSC



13. Ordering Information

13.1 TSC80251G2D ROMless

TEMIC Part Number	ROM	Description	
High Speed Versions 4.5 to 5.5 V, Commercial and Industrial			
TSC80251G2D-16CB	ROMless	16 MHz, Commercial 0° to 70°C, PLCC 44	
TSC80251G2D-24CB	ROMless	24 MHz, Commercial 0° to 70°C, PLCC 44	
TSC80251G2D-24CED	ROMless	24 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾	
TSC80251G2D-24IA	ROMless	24 MHz, Industrial -40° to 85°C, PDIL 40	
TSC80251G2D-24IB	ROMless	24 MHz, Industrial -40° to 85°C, PLCC 44	
Low Voltage Versions 2.7 to 5.5 V, Commercial			
TSC80251G2D-L16CB	ROMless	16 MHz, Commercial, PLCC 44	
TSC80251G2D-L16CED	ROMless	16 MHz, Commercial, VQFP 44, Dry pack ⁽¹⁾	
		·	

Note:

1. Dry Pack mandatory for VQFP package.

13.2 TSC83251G1D 16 Kbytes Mask ROM

TEMIC Part Number ⁽²⁾	ROM	Description	
High Speed Versions 4.5 to 5.5 V, Commercial and Industrial			
TSC251G1Dxxx-16CB	16K MaskROM	16 MHz, Commercial 0° to 70°C, PLCC 44	
TSC251G1Dxxx-24CB	16K MaskROM	24 MHz, Commercial 0° to 70°C, PLCC 44	
TSC251G1Dxxx-24CED	16K MaskROM	24 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾	
TSC251G1Dxxx-24IA	16K MaskROM	24 MHz, Industrial -40° to 85°C, PDIL 40	
TSC251G1Dxxx-24IB	16K MaskROM	24 MHz, Industrial -40° to 85°C, PLCC 44	
Low Voltage Versions 2.7 to 5.5 V, Commercial			
TSC251G1Dxxx-L16CB	16K MaskROM	16 MHz, Commercial 0° to 70°C, PLCC 44	
TSC251G1Dxxx-L16CED	16K MaskROM	16 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾	

Notes:

1. Dry Pack mandatory for VQFP package.

2. xxx: means ROM code, is Cxxx in case of encrypted code.

13.3 TSC83251G2D 32 Kbytes MaskROM

ROM	Description		
High Speed Versions 4.5 to 5.5 V, Commercial and Industrial			
32K MaskROM	16 MHz, Commercial 0° to 70°C, PLCC 44		
32K MaskROM	24 MHz, Commercial 0° to 70°C, PLCC 44		
32K MaskROM	24 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾		
32K MaskROM	24 MHz, Industrial -40° to 85°C, PDIL 40		
32K MaskROM	24 MHz, Industrial -40° to 85°C, PLCC 44		
Low Voltage Versions 2.7 to 5.5 V, Commercial			
32K MaskROM	16 MHz, Commercial 0° to 70°C, PLCC 44		
32K MaskROM	16 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾		
	Prcial and Industria 32K MaskROM 32K MaskROM 32K MaskROM 32K MaskROM 32K MaskROM Percial 32K MaskROM		

Notes:

1. Dry Pack mandatory for VQFP package.

2. xxx: means ROM code, is Cxxx in case of encrypted code.

13.4 TSC87251G2D OTPROM

TEMIC Part Number	ROM	Description	
High Speed Versions 4.5 to 5.5 V, Commercial and Industrial			
TSC87251G2D-16CB	32K OTPROM	16 MHz, Commercial 0° to 70°C, PLCC 44	
TSC87251G2D-24CB	32K OTPROM	24 MHz, Commercial 0° to 70°C, PLCC 44	
TSC87251G2D-24CED	32K OTPROM	24 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾	
TSC87251G2D-24IA	32K OTPROM	24 MHz, Industrial -40° to 85°C, PDIL 40	
TSC87251G2D-24IB	32K OTPROM	24 MHz, Industrial -40° to 85°C, PLCC 44	
Low Voltage Versions 2.7 to 5.5 V, Commercial			
TSC87251G2D-L16CB	32K OTPROM	16 MHz, Commercial 0° to 70°C, PLCC 44	
TSC87251G2D-L16CED	32K OTPROM	16 MHz, Commercial 0° to 70°C, VQFP 44, Dry pack ⁽¹⁾	
	1		

Note:

1. Dry Pack mandatory for VQFP package.

13.5 TSC87251G2D EPROM - UV Window package

TEMIC Part Number	ROM	Description	
High Speed Versions 4.5 to 5.5 V, Industrial			
TSC87251G2D-24IC	32K EPROM	24 MHz, Industrial -40° to 85°C, window CQPJ 44	
TSC87251G2D-24IJ	32K EPROM	24 MHz, Industrial -40° to 85°C, window CDIL 40	
Low Voltage Versions 2.7 to 5.5 V, Industrial			
TSC87251G2D-L16IC	32K EPROM	16 MHz, Commercial -40° to 85°C, window CQPJ 44	

13.6 Options (Please consult TEMIC sales)

- ROM code encryption
- Tape & Real or Dry Pack
- Known good dice
- Ceramic packages
- Extended temperature range: -55°C to +125°C

13.7 Starter Kit

TEMIC Part Number	Description
TSC80251-SK	TSC80251 Starter Kit

13.8 Products Marking

	ROMless versions	Mask ROM versions	OTP versions
[TEMIC	TEMIC	TEMIC
	Temic Part number ⁽¹⁾	Customer Part number	Temic Part number ⁽¹⁾
		Temic Part number	
	© INTEL'97	∞ © INTEL'97	∞ © INTEL'97
	YYWW . Lot Number	YYWW . Lot Number	YYWW . Lot Number

Note:

1. Dry Pack letter (D) not included in the marking.

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